

Connecting via Winsock to STN

Welcome to STN International! Enter x:x

LOGINID:sssptal621con

PASSWORD:

TERMINAL (ENTER 1, 2, 3, OR ?):2

* * * * * Welcome to STN International * * * * *

NEWS	1		Web Page for STN Seminar Schedule - N. America
NEWS	2	JAN 02	STN pricing information for 2008 now available
NEWS	3	JAN 16	CAS patent coverage enhanced to include exemplified prophetic substances
NEWS	4	JAN 28	USPATFULL, USPAT2, and USPATOLD enhanced with new custom IPC display formats
NEWS	5	JAN 28	MARPAT searching enhanced
NEWS	6	JAN 28	USGENE now provides USPTO sequence data within 3 days of publication
NEWS	7	JAN 28	TOXCENTER enhanced with reloaded MEDLINE segment
NEWS	8	JAN 28	MEDLINE and LMEMLINE reloaded with enhancements
NEWS	9	FEB 08	STN Express, Version 8.3, now available
NEWS	10	FEB 20	PCI now available as a replacement to DPCI
NEWS	11	FEB 25	IFIREF reloaded with enhancements
NEWS	12	FEB 25	IMSPRODUCT reloaded with enhancements
NEWS	13	FEB 29	WPINDEX/WPIDS/WPIX enhanced with ECLA and current U.S. National Patent Classification
NEWS	14	MAR 31	IFICDB, IFIPAT, and IFIUIDB enhanced with new custom IPC display formats
NEWS	15	MAR 31	CAS REGISTRY enhanced with additional experimental spectra
NEWS	16	MAR 31	CA/CAPLUS and CASREACT patent number format for U.S. applications updated
NEWS	17	MAR 31	LPCI now available as a replacement to LDPCI
NEWS	18	MAR 31	EMBASE, EMBAL, and LEMBASE reloaded with enhancements
NEWS	19	APR 04	STN AnaVist, Version 1, to be discontinued
NEWS	20	APR 15	WPIDS, WPINDEX, and WPIX enhanced with new predefined hit display formats
NEWS	21	APR 28	EMBASE Controlled Term thesaurus enhanced
NEWS	22	APR 28	IMSRESEARCH reloaded with enhancements
NEWS	23	MAY 30	INPAFAMDB now available on STN for patent family searching
NEWS	24	MAY 30	DGENE, PCTGEN, and USGENE enhanced with new homology sequence search option
NEWS	25	JUN 06	EPFULL enhanced with 260,000 English abstracts
NEWS	26	JUN 06	KOREAPAT updated with 41,000 documents
NEWS EXPRESS	FEBRUARY 08 CURRENT WINDOWS VERSION IS V8.3, AND CURRENT DISCOVER FILE IS DATED 20 FEBRUARY 2008		
NEWS HOURS	STN Operating Hours Plus Help Desk Availability		
NEWS LOGIN	Welcome Banner and News Items		
NEWS IPC8	For general information regarding STN implementation of IPC 8		

Enter NEWS followed by the item number or name to see news on that specific topic.

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* * * * * STN Columbus * * * * *

FILE 'HOME' ENTERED AT 17:24:05 ON 10 JUN 2008

=> SFILE REG

SFILE IS NOT A RECOGNIZED COMMAND

The previous command name entered was not recognized by the system.
For a list of commands available to you in the current file, enter
"HELP COMMANDS" at an arrow prompt (=>).

=> FILE REG

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

0.42

0.42

FILE 'REGISTRY' ENTERED AT 17:25:14 ON 10 JUN 2008

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PLEASE SEE "HELP USAGETERMS" FOR DETAILS.

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Property values tagged with IC are from the ZIC/VINITI data file
provided by InfoChem.

STRUCTURE FILE UPDATES: 9 JUN 2008 HIGHEST RN 1026855-74-2

DICTIONARY FILE UPDATES: 9 JUN 2008 HIGHEST RN 1026855-74-2

New CAS Information Use Policies, enter HELP USAGETERMS for details.

TSCA INFORMATION NOW CURRENT THROUGH January 9, 2008.

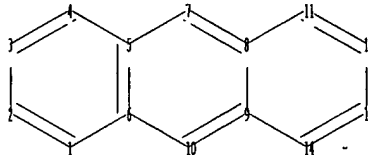
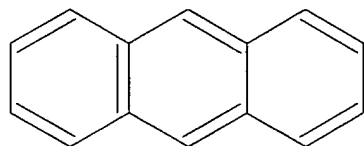
Please note that search-term pricing does apply when
conducting SmartSELECT searches.

REGISTRY includes numerically searchable data for experimental and
predicted properties as well as tags indicating availability of
experimental property data in the original document. For information
on property searching in REGISTRY, refer to:

<http://www.cas.org/support/stngen/stndoc/properties.html>

=>

Uploading C:\Program Files\Stnexp\Queries\SEM.str



ring nodes :

1 2 3 4 5 6 7 8 9 10 11 12 13 14

ring bonds :

1-2 1-6 2-3 3-4 4-5 5-6 5-7 6-10 7-8 8-9 8-11 9-10 9-14 11-12 12-13
13-14

normalized bonds :

1-2 1-6 2-3 3-4 4-5 5-6 5-7 6-10 7-8 8-9 8-11 9-10 9-14 11-12 12-13
13-14

Match level :

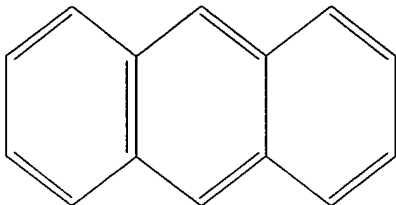
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:Atom
11:Atom 12:Atom 13:Atom 14:Atom

L1 STRUCTURE UPLOADED

=> D L1

L1 HAS NO ANSWERS

L1 STR



Structure attributes must be viewed using STN Express query preparation.

=> S L1 FULL

FULL SEARCH INITIATED 17:25:50 FILE 'REGISTRY'

FULL SCREEN SEARCH COMPLETED - 486996 TO ITERATE

100.0% PROCESSED 486996 ITERATIONS

79682 ANSWERS

SEARCH TIME: 00.00.08

L2 79682 SEA SSS FUL L1

=> FILE CAPLUS

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

178.82

179.24

FILE 'CAPLUS' ENTERED AT 17:26:08 ON 10 JUN 2008

USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.

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FILE COVERS 1907 - 10 Jun 2008 VOL 148 ISS 24

FILE LAST UPDATED: 9 Jun 2008 (20080609/ED)

Effective October 17, 2005, revised CAS Information Use Policies apply. They are available for your review at:

<http://www.cas.org/legal/infopolicy.html>

=> S L2
L3 101687 L2

=>

IS NOT A RECOGNIZED COMMAND

The previous command name entered was not recognized by the system.
For a list of commands available to you in the current file, enter
"HELP COMMANDS" at an arrow prompt (=>).

=>

=> S L3 AND SEMICONDUCTOR
642362 SEMICONDUCTOR
L4 2088 L3 AND SEMICONDUCTOR

=> S L4 AND BINDER
195554 BINDER
L5 26 L4 AND BINDER

=> D L5 IBIB ABS HITSTR 1-26

L5 ANSWER 1 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2008:315927 CAPLUS

DOCUMENT NUMBER: 148:318707

TITLE: Laser-decomposing resin compositions having high
sensitivity and good pattern profiles and their
pattern-forming materials

INVENTOR(S): Taguchi, Takanori

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 53pp.

CODEN: JKXXAF

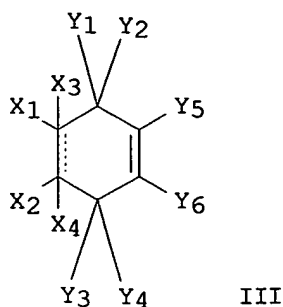
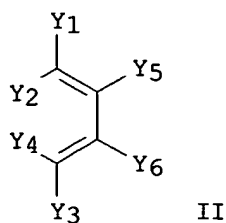
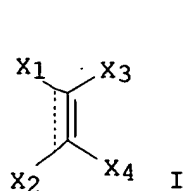
DOCUMENT TYPE: Patent

LANGUAGE: Japanese

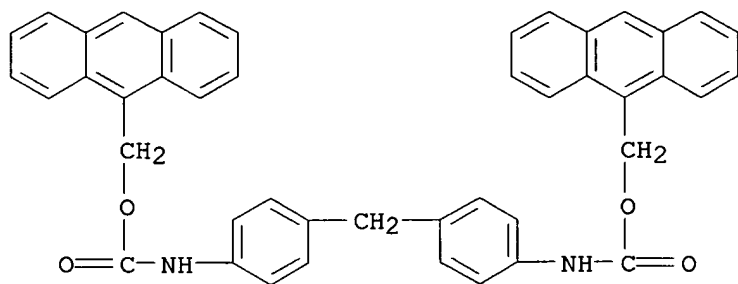
FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2008056888	A	20080313	JP 2007-42844	20070222
PRIORITY APPLN. INFO.:			JP 2006-208397	A 20060731
GI				



- AB The resin compns. contain dienophile compds. and diene compds., and/or adducts of dienophile compds. and diene compds. Preferably, the dienophile compds. comprise I and the diene compds. comprise II (X1-X4, Y1-Y6 = H, monovalent substituent, polyvalent nonmetallic atom. group; X1 and X2, X3 and X4, Y1 and Y3, or Y2 and Y4 may be bonded together and form ring structure). Preferably, the adducts of the dienophile compds. and the diene compds. comprise III (X1-X4, Y1-Y6 = same as above). Laser-decomposing resin compns. containing Diels-Alder reaction products of dienophile compds. and diene compds., preferably, represented by I and II resp. Preferably, the laser-decomposing resin compns. further contain binder polymers and polymerizable compds. The pattern-forming materials comprise substrates having thereon layers of the laser-decomposing resin compns. The patterns are formed by irradiating CO2 laser, semiconductor laser, YAG laser, or fiber laser. The pattern-forming materials may be laser-sensitive flexog. printing original plates.
- IT 1009623-61-3
 RL: MOA (Modifier or additive use); RCT (Reactant); RACT (Reactant or reagent); USES (Uses)
 (laser-decomposing resin compns. having high sensitivity and good pattern profiles and their pattern-forming materials for flexog. printing plates)
- RN 1009623-61-3 CAPLUS
- CN Carbamic acid, N,N'-(methylenedi-4,1-phenylene)bis-, C,C'-bis(9-anthracenylmethyl) ester (CA INDEX NAME)



ACCESSION NUMBER: 2008:121202 CAPLUS
DOCUMENT NUMBER: 148:201707
TITLE: Organic light-emitting material formulation including
a luminescent material housed in a protective porous
matrix material mixed with a binder and a
solvent
INVENTOR(S): Brunacci, Antonio; Jouanique-Dubuis, Cecile
PATENT ASSIGNEE(S): Iee International Electronics & Engineering S.A.,
Luxembourg
SOURCE: Eur. Pat. Appl., 10pp.
CODEN: EPXXDW
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1883124	A1	20080130	EP 2006-117971	20060727
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, AL, BA, HR, MK, YU				

PRIORITY APPLN. INFO.: EP 2006-117971 20060727

AB A formulation of light-emitting material particularly suitable for forming displays and lamps via printing techniques comprises organic light emitting material housed in protective porous matrix material; a binder; and a solvent. The matrix material is selected from microporous and mesoporous materials, such as zeolites, porous oxides, mol. sieves, silicoaluminophosphates and aluminosilicates. Method of manufacturing electroluminescent devices employing the luminescent formulation are also discussed.

IT 62555-84-4
RL: PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)
(light-emitting material; organic light-emitting material formulation including a luminescent material housed in protective porous matrix material mixed with binder and solvent)

RN 62555-84-4 CAPLUS

CN 9H-Carbazole, 3,3'-(9,10-anthracenediyl)di-2,1-ethenediyl)bis[9-ethyl- (CA
INDEX NAME)

KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK,
 MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO,
 RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT,
 TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW
 RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE,
 IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ,
 CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH,
 GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY,
 KG, KZ, MD, RU, TJ, TM

PRIORITY APPLN. INFO.:

EP 2006-1282

A 20060121

AB The invention relates to an improved electronic device, like an organic field emission transistor (OFET), which has a short source to drain channel length and contains an organic semiconducting formulation comprising a semiconducting binder.

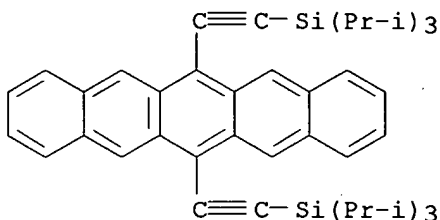
IT 373596-08-8

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(electronic short channel device comprising an organic semiconductor formulation in organic field emission transistors)

RN 373596-08-8 CAPLUS

CN Pentacene, 6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



REFERENCE COUNT:

6

THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 4 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2006:1339367 CAPLUS

DOCUMENT NUMBER: 146:91393

TITLE: Method of patterning nano conductive film

INVENTOR(S): Park, Jong-Jin; Kim, Myeong-Suk; Noh, Tae-Yong; Lee, Sung-Hun; Lee, Sang-Yoon; Jeong, Eun-Jeong

PATENT ASSIGNEE(S): S. Korea

SOURCE: U.S. Pat. Appl. Publ., 11pp.

CODEN: USXXCO

DOCUMENT TYPE: Patent

LANGUAGE: English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20060284169	A1	20061221	US 2006-394085	20060331
KR 2006132396	A	20061221	KR 2005-52721	20050618
CN 1881642	A	20061220	CN 2006-10073281	20060407
JP 2006351543	A	20061228	JP 2006-167517	20060616
PRIORITY APPLN. INFO.:			KR 2005-52721	A 20050618

OTHER SOURCE(S): MARPAT 146:91393

AB A donor substrate for forming a nano conductive film includes a base substrate and a transferring layer that is disposed on the base substrate. The transferring layer includes nano conductive particles and an organic semiconductor. A method of patterning a nano conductive film is provided, wherein a donor substrate in which nano conductive particles are

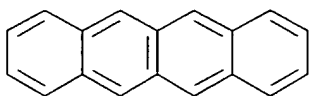
dispersed by employing an organic semiconductor having low mol. weight as a binder was prepared, and nano conductive particles are patterned on a receptor substrate by employing the donor substrate. The method can be used to prepare patterns of various devices including a display device such as an OLED and an OTFT. Such a device can be prepared simply and economically by preparing a device comprising nano conductive particles and an organic semiconductor in wet basis even without deposition.

IT 92-24-0D, Tetracene, derivs. 120-12-7D, Anthracene, derivs. 135-48-8D, Pentacene, derivs. 191-07-1, Coronene 191-07-1D, Coronene, derivs. 517-51-1, Rubrene 517-51-1D, Rubrene, derivs.

RL: PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)
(method of patterning nano conductive film for semiconductor devices)

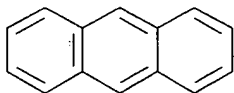
RN 92-24-0 CAPLUS

CN Naphthacene (CA INDEX NAME)



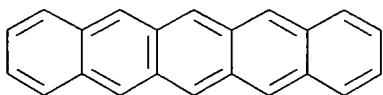
RN 120-12-7 CAPLUS

CN Anthracene (CA INDEX NAME)



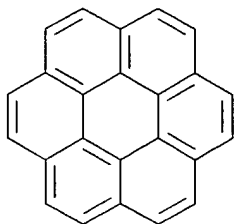
RN 135-48-8 CAPLUS

CN Pentacene (CA INDEX NAME)



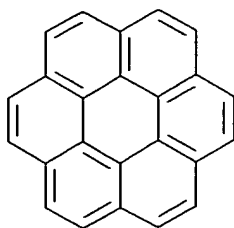
RN 191-07-1 CAPLUS

CN Coronene (CA INDEX NAME)

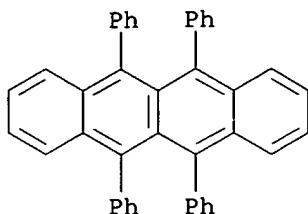


RN 191-07-1 CAPLUS

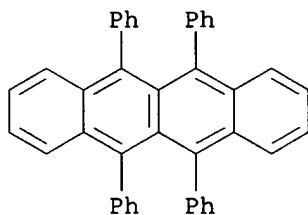
CN Coronene (CA INDEX NAME)



RN 517-51-1 CAPLUS
CN Naphthalene, 5,6,11,12-tetraphenyl- (CA INDEX NAME)



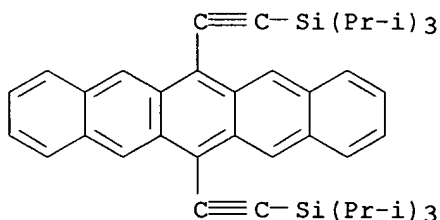
RN 517-51-1 CAPLUS
CN Naphthalene, 5,6,11,12-tetraphenyl- (CA INDEX NAME)



L5 ANSWER 5 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
ACCESSION NUMBER: 2006:437554 CAPLUS
DOCUMENT NUMBER: 144:479184
TITLE: Process for making an organic field effect transistor with areas of reduced carrier mobility
INVENTOR(S): Brown, Beverley Anne; Veres, Janos; Ogier, Simon Dominic
PATENT ASSIGNEE(S): Merck Patent G.m.b.H., Germany
SOURCE: PCT Int. Appl., 24 pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2006048092	A1	20060511	WO 2005-EP10661	20051004
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG,				

SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN,
YU, ZA, ZM, ZW
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE,
IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ,
CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY,
KG, KZ, MD, RU, TJ, TM
EP 1807884 A1 20070718 EP 2005-790320 20051004
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE,
IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR
JP 2008519445 T 20080605 JP 2007-539481 20051004
KR 2007083921 A 20070824 KR 2007-710026 20070502
US 20070259477 A1 20071108 US 2007-666751 20070502
PRIORITY APPLN. INFO.: GB 2004-24342 A 20041103
WO 2005-EP10661 W 20051004
AB The present invention relates to a process for reducing the mobility of an
organic semiconductor (OSC) layer in an electronic device having a
semiconducting channel area. The mobility of the OSC is reduced in
specific areas outside the channel area by applying an oxidizing agent to
the OSC layer.
IT 373596-08-8
RL: DEV (Device component use); USES (Uses)
(organic semiconductor layer; process for making an organic field
effect transistor with areas of reduced carrier mobility)
RN 373596-08-8 CAPLUS
CN Pentacene, 6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



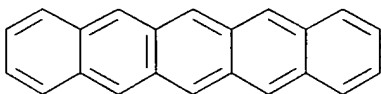
REFERENCE COUNT: 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS
RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L5 ANSWER 6 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
ACCESSION NUMBER: 2006:49396 CAPLUS
DOCUMENT NUMBER: 144:140478
TITLE: Method for fabricating semiconductor element
from dispersion of semiconductor particles
INVENTOR(S): Kugler, Thomas; Newsome, Christopher; Russel, David;
Li, Shunpu
PATENT ASSIGNEE(S): Seiko Epson Corporation, Japan
SOURCE: U.S. Pat. Appl. Publ., 10 pp.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20060014365	A1	20060119	US 2005-125138	20050510
GB 2416428	A	20060125	GB 2004-16124	20040719
KR 2006046268	A	20060517	KR 2005-45497	20050530
JP 2006041495	A	20060209	JP 2005-180203	20050621
CN 1725455	A	20060125	CN 2005-10083398	20050718

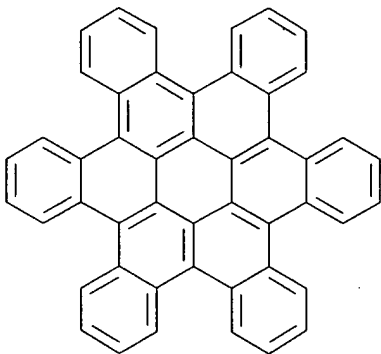
AB Provided is a method for forming a semiconductor element such as film. The method comprises the steps of: (i) depositing a suspension of particles of a first semiconductor and a solution of a second semiconductor or a precursor thereof on a surface of a substrate such that a mixture comprising the particles of the first semiconductor suspended in a liquid phase comprising the second semiconductor or precursor thereof results thereon; and (ii) solidifying the mixture to form the semiconductor element comprising particles of the first semiconductor in a matrix of the second semiconductor which elec. connects adjacent particles of the first semiconductor, the first and second semiconductors being of the same conductivity type and being formed from either the same or different materials. The method does not require any step of vacuum deposition or sintering. Also provided is a semiconductor element itself. The element comprises semiconductor particles in a matrix of a semiconductor binder that has the same conductivity type as the semiconductor particles and which is the same or a different material than that forming the particles, the semiconductor binder elec. connecting adjacent semiconductor particles. The above stated semiconductor film is formed in fabrication of thin-film transistor, organic light-emitting element, etc.

IT 135-48-8, Pentacene 1065-80-1, Hexabenzocoronene
RL: DEV (Device component use); PRP (Properties); USES (Uses)
(fabricating of semiconductor element from dispersion of semiconductor particles)

RN 135-48-8 CAPLUS
CN Pentacene (CA INDEX NAME)



RN 1065-80-1 CAPLUS
CN Hexabenzocoronene [a,d,g,j,m,p] (CA INDEX NAME)



L5 ANSWER 7 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
ACCESSION NUMBER: 2005:1005014 CAPLUS
DOCUMENT NUMBER: 143:317185
TITLE: Solid electrolytic capacitor and the use thereof
INVENTOR(S): Naito, Kazumi; Tamura, Katutoshi
PATENT ASSIGNEE(S): Showa Denko K.K., Japan
SOURCE: PCT Int. Appl., 35 pp.
CODEN: PIXXD2

DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

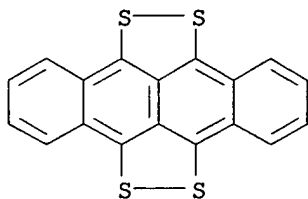
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2005086191	A1	20050915	WO 2005-JP4414	20050308
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW,				
RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
JP 2005294817	A	20051020	JP 2005-63275	20050308
CN 1930647	A	20070314	CN 2005-80007507	20050308
US 20070206344	A1	20070906	US 2006-592377	20060911
PRIORITY APPLN. INFO.:				
			JP 2004-65072	A 20040309
			US 2004-553529P	P 20040317
			WO 2005-JP4414	W 20050308

AB The present invention relates to a solid electrolytic capacitor with low ESR obtained by stacking a dielec. layer on a surface of an anode body comprising a valve-acting metal or an elec. conducting oxide, further sequentially stacking a semiconductor layer and an elec. conducting layer on the dielec. layer to prepare a solid electrolytic capacitor element, and molding it with a jacket material, the elec. conducting layer having an elec. conducting paste layer mainly comprising an elec. conducting metal powder and resin, wherein the tap d. of the elec. conducting metal powder is 4 g/cm³ or more, and an electronic circuit and an electronic device using the solid electrolytic capacitor.

IT 193-44-2, Tetrathiotetracene
RL: PEP (Physical, engineering or chemical process); PYP (Physical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)
(fabrication of solid electrolytic capacitor with low equivalent series resistance)

RN 193-44-2 CAPLUS

CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (CA INDEX NAME)



REFERENCE COUNT: 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 8 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2005:523782 CAPLUS

DOCUMENT NUMBER: 143:69829

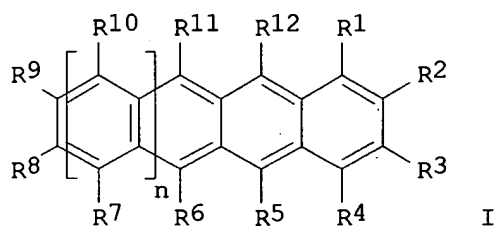
TITLE: Improvements in and relating to organic semiconducting layers

INVENTOR(S): Brown, Beverley Anne; Veres, Janos; Anemian, Remi

Manouk; Williams, Richard Thomas; Ogier, Simon
Dominic; Leeming, Stephen William
PATENT ASSIGNEE(S): Avecia Limited, UK
SOURCE: PCT Int. Appl., 68 pp.
CODEN: PIXXD2
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2005055248	A2	20050616	WO 2004-GB4973	20041125
WO 2005055248	A3	20050728		
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
EP 1687830	A2	20060809	EP 2004-819715	20041125
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, FI, RO, CY, TR, BG, CZ, EE, HU, PL, SK, IS				
EP 1783781	A2	20070509	EP 2007-2498	20041125
EP 1783781	A3	20071003		
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR				
JP 2007519227	T	20070712	JP 2006-540612	20041125
EP 1808866	A1	20070718	EP 2007-4534	20041125
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR				
US 20070102696	A1	20070510	US 2006-580552	20060526
US 20070137520	A1	20070621	US 2007-671877	20070206
US 20080009625	A1	20080110	US 2007-822594	20070709
PRIORITY APPLN. INFO.:				
			GB 2003-27654	A 20031128
			GB 2004-7852	A 20040407
			GB 2004-14347	A 20040626
			EP 2004-819715	A3 20041125
			WO 2004-GB4973	W 20041125
			US 2006-580552	A3 20060526

OTHER SOURCE(S): MARPAT 143:69829
GI



AB An organic semiconducting layer formulation (I), which comprises: an organic binder which has a permittivity, ϵ , at 1,000 Hz of 3.3 or less; and a polyacene compound of Formula: A: wherein: each of R1, R2, R3,

R4, R5, R6, R7, R8, R9, R10, R11 and R12, which may be the same or different, independently represents hydrogen; an optionally substituted C1-C40 carbyl or hydrocarbyl group; an optionally substituted C1-C40 alkoxy group; an optionally substituted C6-C40 aryloxy group; an optionally substituted C7-C40 alkylaryloxy group; an optionally substituted C2-C40 alkoxy carbonyl group; an optionally substituted C7-C40 aryloxy carbonyl group; a cyano group (-CN); a carbamoyl group (-C(=O)NH2); a haloformyl group (-C(=O)-X, wherein X represents a halogen atom); a formyl group (-C(=O)-H); an isocyano group; an isocyanate group; a thiocyanate group or a thioisocyanate group; an optionally substituted amino group; a hydroxy group. A nitro group; a CF3 group; a halo group (Cl, Br, F); or an optionally substituted silyl group; and wherein independently each pair of R2 and R3 and/or R8 and R9, may be cross-bridged to form a C4-C40 saturated or unsatd. ring, which saturated or unsatd. ring may be intervened by an oxygen atom, a sulfur atom or a group shown by formula -N(Ra)- (wherein Ra is a hydrogen atom or an optionally substituted hydrocarbon group), or may optionally be substituted; and wherein one or more of the carbon atoms of the polyacene skeleton may optionally be substituted by a heteroatom selected from N, P, As, O, S, Se and Te; and wherein independently any two or more of the substituents R1-R12 which are located on adjacent ring positions of the polyacene may, together, optionally constitute a further C4-C40 saturated or unsatd. ring optionally interrupted by O, S or -N(Ra) where Ra is as defined above or an aromatic ring system, fused to the polyacene; and wherein n is 0, 1, 2, 3 or 4, also claimed is an electronic device, particularly.

IT 6006-83-3, 5,14-Pentacenedione 317809-68-0

373596-08-8 373596-09-9 398128-81-9

775324-33-9 775324-34-0 854519-90-7

854519-91-8 854519-92-9 854519-95-2

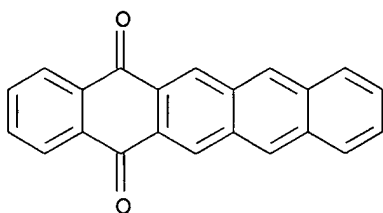
854519-96-3 854520-00-6

RL: DEV (Device component use); USES (Uses)

(improvements in and relating to organic semiconducting layers for organic FETs)

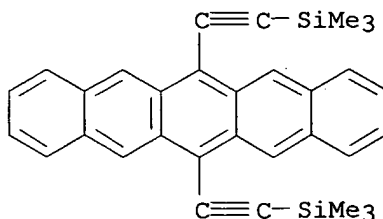
RN 6006-83-3 CAPLUS

CN 5,14-Pentacenedione (CA INDEX NAME)



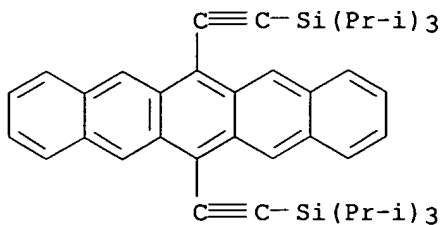
RN 317809-68-0 CAPLUS

CN Pentacene, 6,13-bis[2-(trimethylsilyl)ethynyl]- (CA INDEX NAME)



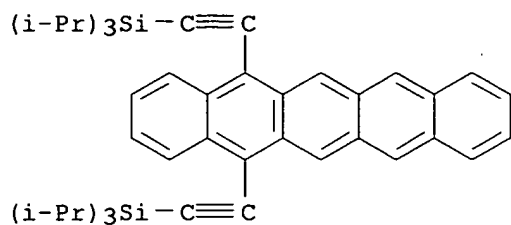
RN 373596-08-8 CAPLUS

CN Pentacene, 6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



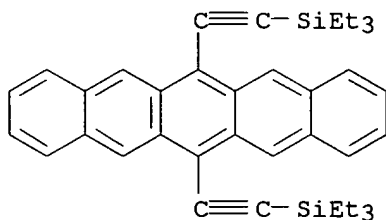
RN 373596-09-9 CAPLUS

CN Pentacene, 5,14-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



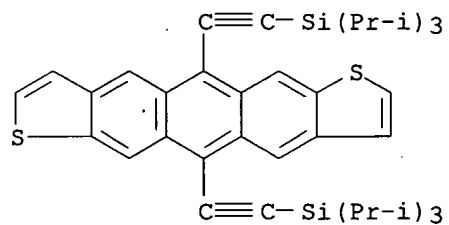
RN 398128-81-9 CAPLUS

CN Pentacene, 6,13-bis[2-(triethylsilyl)ethynyl]- (CA INDEX NAME)



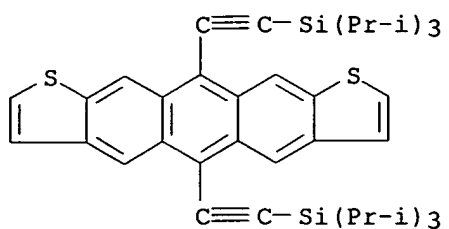
RN 775324-33-9 CAPLUS

CN Anthra[2,3-b:6,7-b']dithiophene, 5,11-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



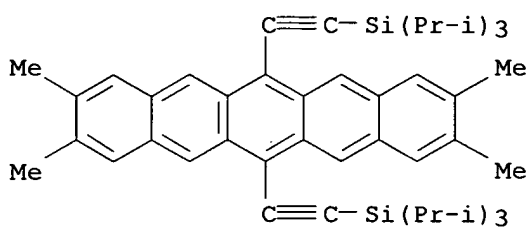
RN 775324-34-0 CAPLUS

CN Silane, (anthra[2,3-b:7,6-b']dithiophene-5,11-diyl)di-2,1-ethynediyl)bis[tris(1-methylethyl)- (9CI) (CA INDEX NAME)



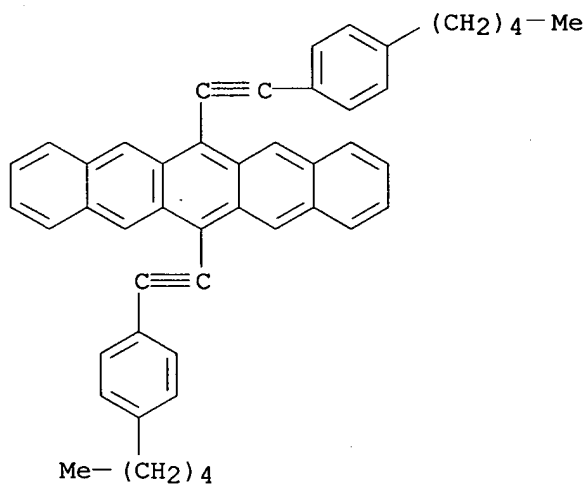
RN 854519-90-7 CAPLUS

CN Pentacene, 2,3,9,10-tetramethyl-6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



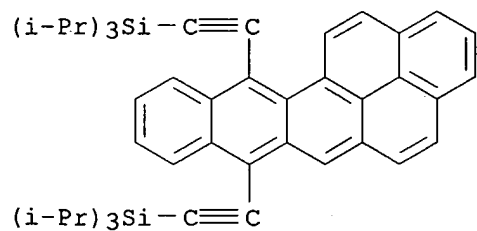
RN 854519-91-8 CAPLUS

CN Pentacene, 6,13-bis[2-(4-pentylphenyl)ethynyl]- (CA INDEX NAME)

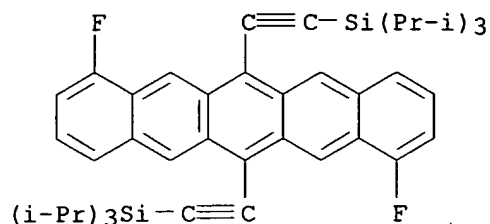


RN 854519-92-9 CAPLUS

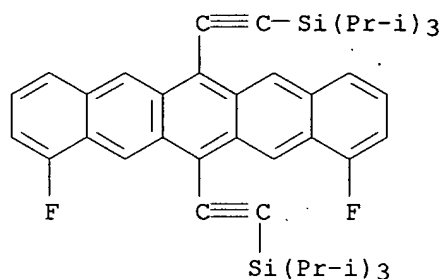
CN Dibenzo[1,pqr]benz[a]anthracene, 7,12-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



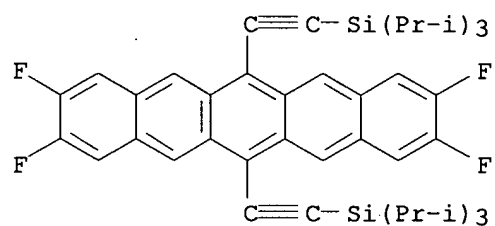
RN 854519-95-2 CAPLUS
CN Pentacene, 1,8-difluoro-6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]-
(CA INDEX NAME)



RN 854519-96-3 CAPLUS
CN Pentacene, 1,11-difluoro-6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]-
(CA INDEX NAME)



RN 854520-00-6 CAPLUS
CN Pentacene, 2,3,9,10-tetrafluoro-6,13-bis[2-[tris(1-methylethyl)silyl]ethynyl]- (CA INDEX NAME)



L5 ANSWER 9 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2004:965525 CAPLUS

DOCUMENT NUMBER: 141:419284

TITLE: Valve acting metal sintered body, production method therefor, and solid electrolytic capacitor

INVENTOR(S): Omori, Kazuhiro; Shibuya, Yoshinori

PATENT ASSIGNEE(S): Showa Denko K.K., Japan

SOURCE: PCT Int. Appl., 112 pp.

CODEN: PIXXD2

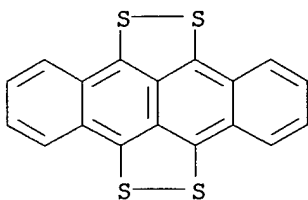
DOCUMENT TYPE: Patent

LANGUAGE: English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2004097870	A1	20041111	WO 2004-JP6102	20040427
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
JP 2004349683	A	20041209	JP 2004-96223	20040329
EP 1618575	A1	20060125	EP 2004-729761	20040427
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK, HR				
CN 1813323	A	20060802	CN 2004-80018186	20040427
US 20060279908	A1	20061214	US 2005-554694	20051027
PRIORITY APPLN. INFO.:			JP 2003-123208	A 20030428
			US 2003-467152P	P 20030502
			WO 2004-JP6102	W 20040427
AB The invention provides a valve-acting metal sintered body for anode of a solid electrolytic capacitor, having a high capacitance, well impregnated with cathode material, and exhibiting excellent properties particularly when having a large volume. The provided capacitor has a low ESR, an excellent tan δ value, and good long-term reliability such as moisture resistance and heat resistance with the sintered body. The production method for the capacitor comprises the following steps: coating/printing/shaping a granulated product of a mixed dispersion containing a pore-forming agent, an organic binder, and a primary powder or secondary aggregated powder of 1 member selected from valve-acting metal, a valve-acting metal compound, and a valve-acting metal alloy or a granulated powder thereof and a solvent; or compressing and shaping the granulated product of a mixture obtained by removing the solvent from the dispersion; sintering the shaped article containing a pore-forming agent; and removing the pore-forming agent from the sintered body.				
IT 193-44-2, Tetrathiotetracene RL: DEV (Device component use); USES (Uses) (organic semiconductor; valve acting metal sintered body, production method therefor, and solid electrolytic capacitor)				
RN 193-44-2 CAPLUS CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (CA INDEX NAME)				



REFERENCE COUNT: 38 THERE ARE 38 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 10 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
 ACCESSION NUMBER: 2004:533195 CAPLUS
 DOCUMENT NUMBER: 141:79294
 TITLE: Semiconductor compositions and electrophotographic apparatus parts using them with

INVENTOR(S): Yoshikawa, Hitoshi; Iinuma, Sumio
 PATENT ASSIGNEE(S): Tokai Rubber Industries, Ltd., Japan
 SOURCE: Jpn. Kokai Tokkyo Koho, 35 pp.
 CODEN: JKXXAF
 DOCUMENT TYPE: Patent
 LANGUAGE: Japanese
 FAMILY ACC. NUM. COUNT: 1
 PATENT INFORMATION:

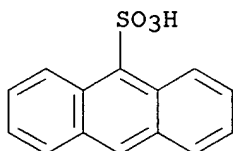
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004184513	A	20040702	JP 2002-348351	20021129
JP 3960215	B2	20070815		
PRIORITY APPLN. INFO.:			JP 2002-348351	20021129

OTHER SOURCE(S): MARPAT 141:79294

AB The comps., development rolls for electrophotog., contain elec. conductive polymers (A) having surfactant structures (sulfonic acid group-containing naphthalene or anthracene structures, preferably) and showing solubility to PhMe or Me Et ketone ≥20% and solubility to water <3% and binder polymers (B), thus improving compatibility of them.

IT 22582-76-9DP, 9-Anthracenesulfonic acid, polymers with aniline
 RL: DEV (Device component use); IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (conductive polymer; semiconductor comps. containing conductive surfactant polymers with good heat, moisture, and voltage resistance for electrophotog. apparatus)

RN 22582-76-9 CAPLUS
 CN 9-Anthracenesulfonic acid (CA INDEX NAME)



L5 ANSWER 11 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
 ACCESSION NUMBER: 2004:142824 CAPLUS
 DOCUMENT NUMBER: 140:208704
 TITLE: Crosslinkable fill compositions for uniformly protecting via and contact holes
 INVENTOR(S): Lamb, James E.; Shao, Xie
 PATENT ASSIGNEE(S): USA
 SOURCE: U.S. Pat. Appl. Publ., 22 pp., Cont.-in-part of U.S. Ser. No. 196,603.
 CODEN: USXXCO
 DOCUMENT TYPE: Patent
 LANGUAGE: English
 FAMILY ACC. NUM. COUNT: 2
 PATENT INFORMATION:

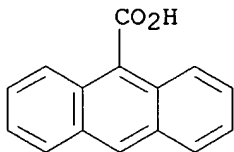
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20040034134	A1	20040219	US 2003-643398	20030819
US 20010056144	A1	20011227	US 2001-918110	20010730
US 20020041953	A1	20020411	US 2001-931264	20010816
US 20020016057	A1	20020207	US 2001-966208	20010927
US 20020183426	A1	20021205	US 2002-196603	20020715
US 20030148601	A1	20030807	US 2003-366963	20030214

US 20040147108	A1	20040729	US 2004-759447	20040116
US 7026237	B2	20060411		
US 20050159520	A1	20050721	US 2004-964288	20041013
PRIORITY APPLN. INFO.:			US 1999-383785	B1 19990826
			US 2000-632823	B1 20000807
			US 2001-918110	A1 20010730
			US 2002-196603	A2 20020715
			US 1999-440399	B1 19991115
			US 1999-460162	A1 19991213
			US 2001-966208	B1 20010927
			US 2003-366963	A1 20030214
			US 2003-643398	B1 20030819

AB The present invention is broadly concerned with fill compns. and methods useful for protecting the surfaces forming the contact and via holes during dual damascene processes for the production of integrated circuits. More particularly, the compns. of the invention comprise a quantity of solid crosslinkable components including a polymer binder, and a solvent system for the solid components. A via and contact hole fill composition and method for using the composition in the dual damascene production of circuits is provided. Broadly, the fill compns. include a quantity of solid components including a polymer binder and a solvent system for the solid components. The b.p. of the solvent system is less than the crosslinking temperature of the composition Preferred solvents for use in the solvent system include those selected from the group consisting of alcs., ethers, glycol ethers, amides, ketones, and mixts. thereof. Preferred polymer binders are those having an aliphatic backbone and a mol. weight of .ltorsim.80,000, with polyesters being particularly preferred. In use, the fill composition is applied to the substrate surfaces forming the contact or via holes as well as to the substrate surfaces surrounding the holes, followed by heating to the composition reflow temperature so as to cause the composition to uniformly flow into and cover the hole-forming surfaces and substrate surfaces. The composition is then cured, and the remainder of the dual damascene process is carried out.

IT 723-62-6, 9-Anthracenecarboxylic acid
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PYP (Physical process); PROC (Process); USES (Uses)
 (in preparation of polymeric fill material for protecting via and contact hole surfaces during dual damascene processes for integrated-circuit fabrication)

RN 723-62-6 CAPLUS
 CN 9-Anthracenecarboxylic acid (CA INDEX NAME)



L5 ANSWER 12 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2004:78554 CAPLUS

DOCUMENT NUMBER: 140:154111

TITLE: Electroluminescent device and methods for its production and use

INVENTOR(S): Kinlen, Patrick J.

PATENT ASSIGNEE(S): Crosslink Polymer Research, USA

SOURCE: U.S. Pat. Appl. Publ., 22 pp., Cont.-in-part of U.S. Ser. No. 207,576.

CODEN: USXXCO

DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 2
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20040018382	A1	20040129	US 2003-352476	20030128
US 7361413	B2	20080422		
US 20040018379	A1	20040129	US 2002-207576	20020729
US 7029763	B2	20060418		
CA 2493153	A1	20040205	CA 2003-2493153	20030718
WO 2004011250	A1	20040205	WO 2003-US22473	20030718
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
AU 2003256608	A1	20040216	AU 2003-256608	20030718
EP 1542867	A1	20050622	EP 2003-771654	20030718
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, SK				
JP 2005535077	T	20051117	JP 2004-524640	20030718
PRIORITY APPLN. INFO.:			US 2002-207576	A2 20020729
			US 2003-352476	A 20030128
			WO 2003-US22473	W 20030718

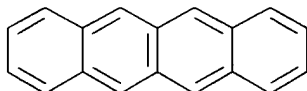
AB A luminescent device is described comprises an electroluminescent phosphor in operative contact with a light-emitting material wherein excitation of the electroluminescent phosphor by an a.c. elec. field causes the emission of light by the light-emitting material, and wherein the electrodes may comprise an intrinsically conductive polymer. Methods of fabricating the device and using it in an electroluminescent display are also described.

IT 92-24-0, Tetracene 120-12-7, Anthracene, uses
62555-84-4 474975-19-4 474975-22-9

RL: DEV (Device component use); USES (Uses)
(light-emitting material; a.c.-powered electroluminescent device and fabrication method)

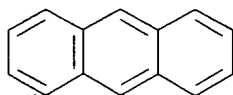
RN 92-24-0 CAPLUS

CN Naphthacene (CA INDEX NAME)



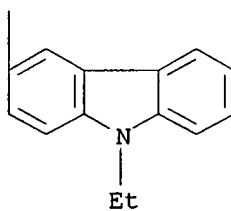
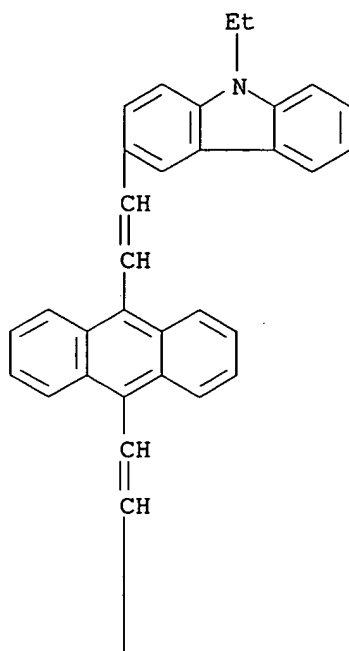
RN 120-12-7 CAPLUS

CN Anthracene (CA INDEX NAME)



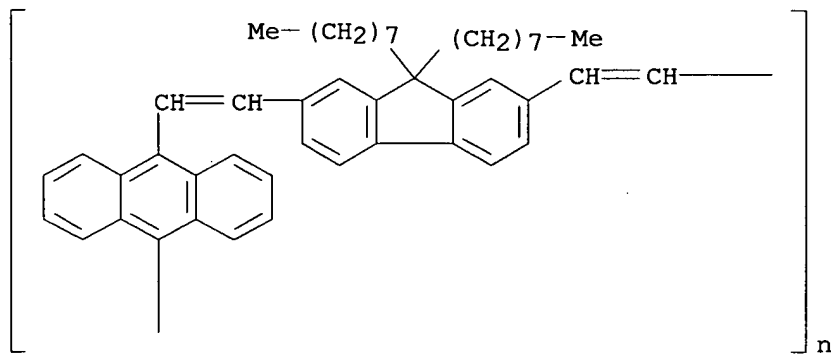
RN 62555-84-4 CAPLUS

CN 9H-Carbazole, 3,3'-(9,10-anthracenediyl-di-2,1-ethenediyl)bis[9-ethyl- (CA INDEX NAME)



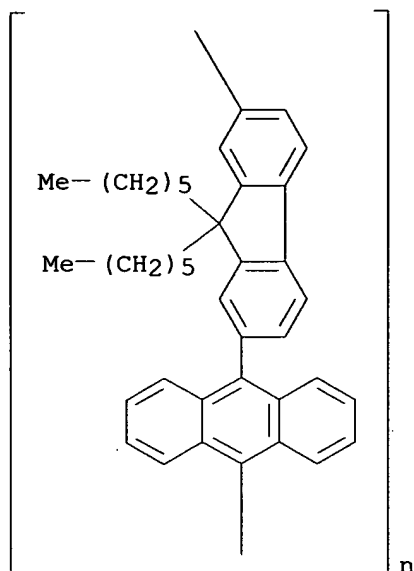
RN 474975-19-4 CAPLUS

CN Poly[9,10-anthracenediyl-1,2-ethenediyl (9,9-dioctyl-9H-fluorene-2,7-diyl)-1,2-ethenediyl] (CA INDEX NAME)



RN 474975-22-9 CAPLUS

CN Poly[9,10-anthracenediyl (9,9-dihexyl-9H-fluorene-2,7-diyl)] (CA INDEX NAME)



REFERENCE COUNT: 94 THERE ARE 94 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 13 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
 ACCESSION NUMBER: 2004:78550 CAPLUS
 DOCUMENT NUMBER: 140:154092
 TITLE: Light-emitting phosphor particles and electroluminescent devices employing same
 INVENTOR(S): Kinlen, Patrick J.
 PATENT ASSIGNEE(S): USA
 SOURCE: U.S. Pat. Appl. Publ., 18 pp.
 CODEN: USXXCO
 DOCUMENT TYPE: Patent
 LANGUAGE: English
 FAMILY ACC. NUM. COUNT: 2
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 20040018379	A1	20040129	US 2002-207576	20020729
US 7029763	B2	20060418		
US 20040018382	A1	20040129	US 2003-352476	20030128
US 7361413	B2	20080422		
CA 2493153	A1	20040205	CA 2003-2493153	20030718
WO 2004011250	A1	20040205	WO 2003-US22473	20030718
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
AU 2003256608	A1	20040216	AU 2003-256608	20030718
EP 1542867	A1	20050622	EP 2003-771654	20030718
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, SK				

JP 2005535077	T	20051117	JP 2004-524640	20030718
US 20060127670	A1	20060615	US 2006-344934	20060201
US 7303827	B2	20071204		

PRIORITY APPLN. INFO.:

US 2002-207576	A2	20020729
US 2003-352476	A	20030128
WO 2003-US22473	W	20030718

AB Phosphor particles are described which are coated with a light-emitting substance (e.g., a light-emitting polymer and/or a light-emitting small mol.). Methods of preparing the coated phosphors are described which entail coating phosphor particles with a light-emitting material. Electroluminescent displays employing the phosphors are also described. Methods for fabricating electroluminescent displays are described which entail formulating an ink by mixing phosphor particles with ≥ 1 binder polymer; depositing a conducting rear electrode onto a substrate in a pattern; depositing the ink onto the rear electrode to form a layer; optionally depositing a layer containing a light-emitting substance onto the layer; optionally depositing a transparent hole transporting electrode onto the layer; and depositing a front outlining electrode; and depositing connection leads to the rear electrode and the front outlining electrode.

IT 62555-84-4 474975-19-4 474975-22-9

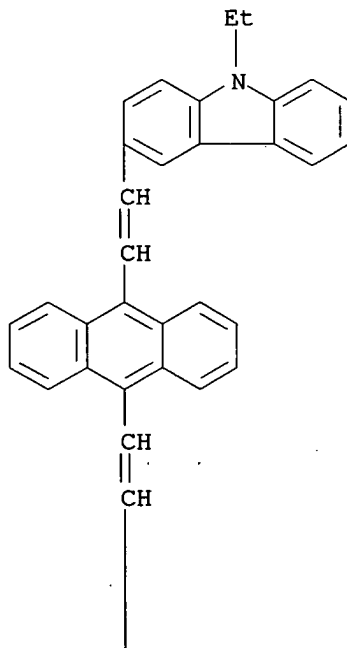
RL: DEV (Device component use); USES (Uses)

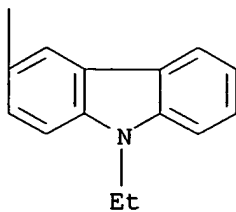
(phosphor particles with light-emitting coatings and their preparation and electroluminescent displays employing them and their fabrication)

RN 62555-84-4 CAPLUS

CN 9H-Carbazole, 3,3'-(9,10-anthracenediyl)di-2,1-ethenediyl)bis[9-ethyl- (CA INDEX NAME)

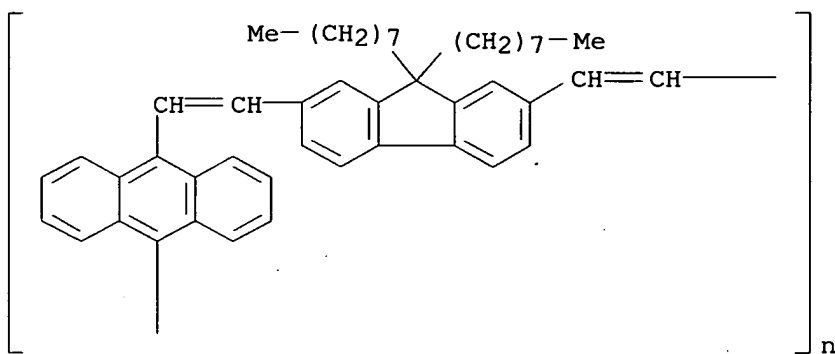
PAGE 1-A





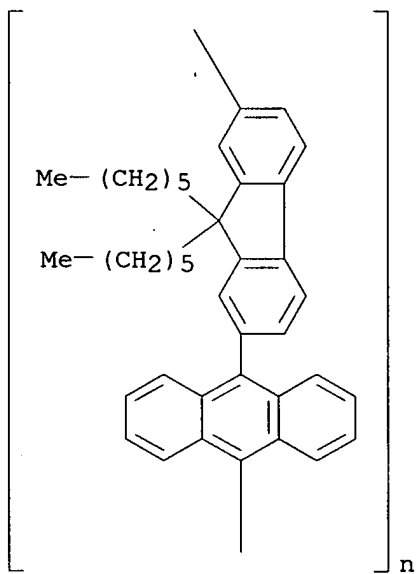
RN 474975-19-4 CAPLUS

CN Poly[9,10-anthracenediyl-1,2-ethenediyl(9,9-dioctyl-9H-fluorene-2,7-diyl)-1,2-ethenediyl] (CA INDEX NAME)



RN 474975-22-9 CAPLUS

CN Poly[9,10-anthracenediyl(9,9-dihexyl-9H-fluorene-2,7-diyl)] (CA INDEX NAME)



REFERENCE COUNT:

91

THERE ARE 91 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 14 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2002:849341 CAPLUS

DOCUMENT NUMBER: 137:377516

TITLE: Electroluminescent devices fabricated with
 encapsulated light emitting polymer particles
 INVENTOR(S): Murasko, Matthew; Kinlen, Patrick J.; St. John, Brent
 PATENT ASSIGNEE(S): Lumimove, Inc., USA
 SOURCE: PCT Int. Appl., 21 pp.
 CODEN: PIXXD2
 DOCUMENT TYPE: Patent
 LANGUAGE: English
 FAMILY ACC. NUM. COUNT: 1
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2002087308	A2	20021107	WO 2002-US13547	20020430
WO 2002087308	A3	20030501		
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
CA 2473969	A1	20021107	CA 2002-2473969	20020430
AU 2002259077	A1	20021111	AU 2002-259077	20020430
US 20030032361	A1	20030213	US 2002-135599	20020430
US 7001639	B2	20060221		
US 20060251798	A1	20061109	US 2005-260738	20051027

PRIORITY APPLN. INFO.:

US 2001-287321P P 20010430
 US 2001-287612P P 20010430
 US 2002-135599 A3 20020430
 WO 2002-US13547 W 20020430

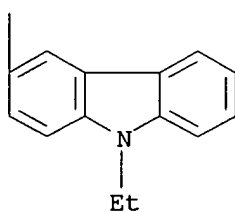
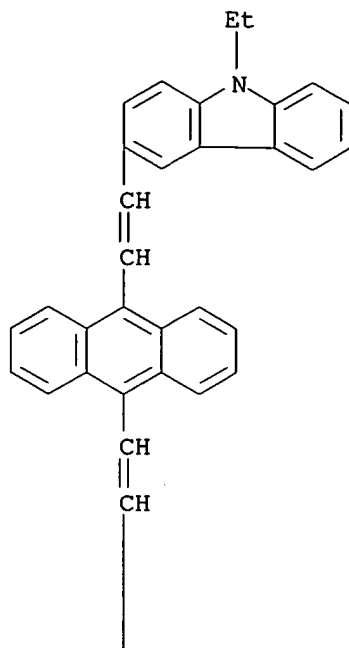
AB Methods for fabricating electroluminescent display devices are described
 which entail encapsulating organic light-emitting material particles with a
 conductive polymer; formulating an ink by mixing the encapsulated
 particles with binder polymers; depositing a conducting rear
 electrode onto a substrate in a pattern; depositing the ink onto rear
 electrode patterns to form a light-emitting layer; depositing a
 transparent hole transporting electrode onto the light-emitting layer;
 depositing a front outlining electrode onto the hole transporting
 electrode; and depositing connection leads to the rear electrode and the
 front outlining electrode.

IT 62555-84-4 474975-19-4 474975-22-9

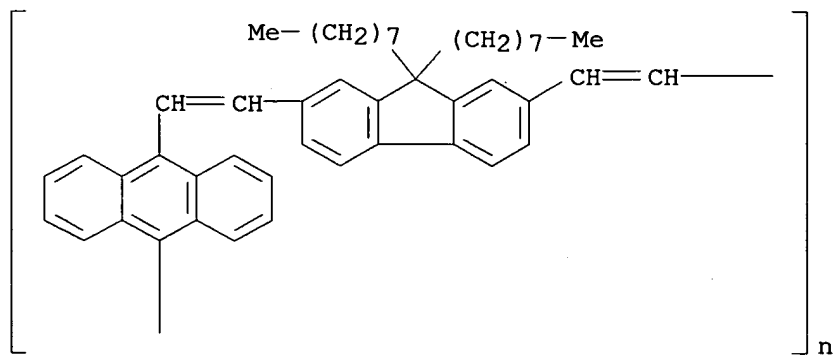
RL: DEV (Device component use); USES (Uses)
 (electroluminescent display fabrication using polymer-encapsulated
 light-emitting particles)

RN 62555-84-4 CAPLUS

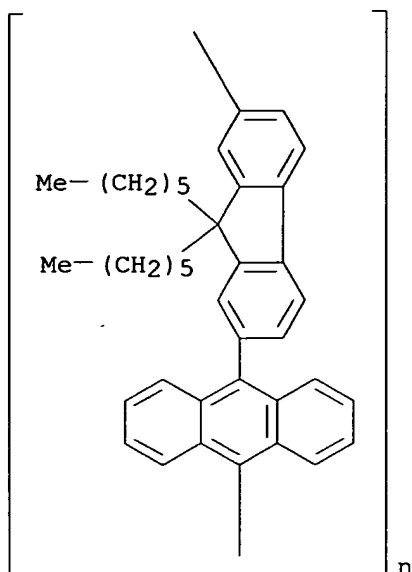
CN 9H-Carbazole, 3,3'-(9,10-anthracenediylldi-2,1-ethenediyl)bis[9-ethyl- (CA
 INDEX NAME)



RN 474975-19-4 CAPLUS
 CN Poly[9,10-anthracenediyl-1,2-ethenediyl (9,9-dioctyl-9H-fluorene-2,7-diyl)-1,2-ethenediyl] (CA INDEX NAME)



RN 474975-22-9 CAPLUS
 CN Poly[9,10-anthracenediyl (9,9-dihexyl-9H-fluorene-2,7-diyl)] (CA INDEX NAME)



L5 ANSWER 15 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2001:798567 CAPLUS

DOCUMENT NUMBER: 135:326222

TITLE: Production method for Niobium sintered body and capacitor

INVENTOR(S): Naito, Kazumi; Kabe, Isao

PATENT ASSIGNEE(S): Showa Denko K.K., Japan

SOURCE: PCT Int. Appl., 27 pp.

CODEN: PIXXD2

DOCUMENT TYPE: Patent

LANGUAGE: English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2001082318	A2	20011101	WO 2001-JP3389	20010420
WO 2001082318	A3	20020613		
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
AU 2001048805	A	20011107	AU 2001-48805	20010420
JP 2002008952	A	20020111	JP 2001-122154	20010420
EP 1275125	A2	20030115	EP 2001-921942	20010420
EP 1275125	B1	20070221		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR				
BR 2001010173	A	20030305	BR 2001-10173	20010420
CN 1507643	A	20040623	CN 2001-808296	20010420
AT 354859	T	20070315	AT 2001-921942	20010420
KR 751267	B1	20070823	KR 2002-714039	20021018
US 20030172774	A1	20030918	US 2003-258122	20030207
US 6835225	B2	20041228		

PRIORITY APPLN. INFO.:

JP 2000-121244 A 20000421
US 2000-233438P P 20000918
WO 2001-JP3389 W 20010420

AB A Nb sintered body which is prepared in such a manner that a Nb powder is sintered at a temperature of 500° to 2000° and allowed to stand at a maximum sintering temperature for 60 min to 150 min in sintering. The Nb sintered body of the present invention is characterized in that (CV) of a capacitance (C) per unit mass and a forming voltage (V) is 90,000 $\mu\text{F.V/g}$ or more, and a value obtained by dividing a product of a mean particle diameter (D50) of a primary particle of the Nb powder and a leakage current (LC) by the CV is $5 \times 10^{-4} \mu\text{m}.\mu\text{A} (\mu\text{F.V})$ or less. And there can be provided a well-balanced capacitor with respect to a preferably low leakage current value regardless of the large capacitance, i.e., a highly reliable capacitance.

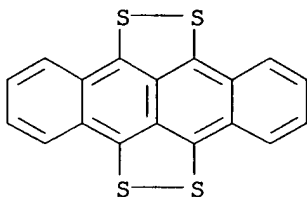
IT 193-44-2, Tetrathiotetracene

RL: DEV (Device component use); USES (Uses)

(organic semiconductor; production method for niobium sintered body and capacitor)

RN 193-44-2 CAPLUS

CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (CA INDEX NAME)



L5 ANSWER 16 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2001:152968 CAPLUS

DOCUMENT NUMBER: 134:187113

TITLE: Improved polymeric fill material for protecting via and contact hole surfaces during dual damascene processes for integrated-circuit fabrication

INVENTOR(S): Lamb, James E., III; Shao, Xie

PATENT ASSIGNEE(S): Brewer Science, USA

SOURCE: PCT Int. Appl., 45 pp.

CODEN: PIXXD2

DOCUMENT TYPE: Patent

LANGUAGE: English

FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2001015211	A1	20010301	WO 2000-US22839	20000817
W:				
AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW				
RW:				
GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
EP 1212788	A1	20020612	EP 2000-955751	20000817
R:				
AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL				
JP 2003508894	T	20030304	JP 2001-519478	20000817

CN 1658375	A	20050824	CN 2005-10009197	20000817
TW 290343	B	20071121	TW 2000-89117234	20000825
US 20020041953	A1	20020411	US 2001-931264	20010816
US 20020016057	A1	20020207	US 2001-966208	20010927
US 20030148601	A1	20030807	US 2003-366963	20030214
US 20040147108	A1	20040729	US 2004-759447	20040116
US 7026237	B2	20060411		

PRIORITY APPLN. INFO.:

US 1999-383785	A	19990826
US 1999-440399	B1	19991115
US 1999-460162	A1	19991213
WO 2000-US22839	W	20000817
US 2001-966208	B1	20010927
US 2003-366963	A1	20030214

AB An improved via and contact hole fill composition and method for using the composition in the dual damascene production of circuits is provided.

Broadly, the

fill compns. include a quantity of solid components including a polymer binder and a solvent system for the solid components. The b.p. of the solvent system is less than the crosslinking temperature of the composition. Preferred solvents for use in the solvent system include those selected from the group consisting of alcs., ethers, glycol ethers, amides, ketones, and mixts. thereof. Preferred polymer binders are those having an aliphatic backbone and a mol. weight of .ltorsim.80,000, with polyesters being particularly preferred. In use, the fill composition is applied to the substrate surfaces forming the contact or via holes as well as to the substrate surfaces surrounding the holes, followed by heating to the composition reflow temperature so as to cause the composition to uniformly

flow into and

cover the hole-forming surfaces and substrate surfaces. The composition is then cured, and the remainder of the dual damascene process is carried out.

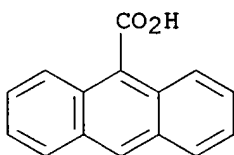
IT 723-62-6, 9-Anthracenecarboxylic acid

RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

(in preparation of polymeric fill material for protecting via and contact hole surfaces during dual damascene processes for integrated-circuit fabrication)

RN 723-62-6 CAPLUS

CN 9-Anthracenecarboxylic acid (CA INDEX NAME)



REFERENCE COUNT:

7

THERE ARE 7 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L5 ANSWER 17 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 2000:665563 CAPLUS

DOCUMENT NUMBER: 133:253993

TITLE: Acrylic antireflective coatings and their manufacture for use in microlithography in fabrication of semiconductor devices

INVENTOR(S): Jung, Min-ho; Hong, Sung-eun; Baik, Ki-ho

PATENT ASSIGNEE(S): Hyundai Electronics Industries Co.,ltd., S. Korea

SOURCE: Ger. Offen., 18 pp.

CODEN: GWXXBX

DOCUMENT TYPE: Patent

LANGUAGE: German

FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 19962663	A1	20000921	DE 1999-19962663	19991223
KR 2000060410	A	20001016	KR 1999-8668	19990315
TW 234689	B	20050621	TW 1999-88120016	19991117
GB 2347927	A	20000920	GB 1999-27834	19991126
GB 2347927	B	20040324		
FR 2791056	A1	20000922	FR 1999-15748	19991214
FR 2791056	B1	20040102		
JP 2000264921	A	20000926	JP 1999-354492	19991214
IT 99TO1092	A1	20010614	IT 1999-TO1092	19991214
IT 1308671	B1	20020109		
CN 1266843	A	20000920	CN 1999-126380	19991215
US 6309790	B1	20011030	US 2000-499873	20000207
NL 1014639	A1	20000918	NL 2000-1014639	20000314
NL 1014639	C2	20011228		

PRIORITY APPLN. INFO.:

KR 1999-8668 A 19990315

AB Acrylic antireflective coatings with higher etching speed in microlithog. using 248 Nm KrF-, 193 Nm ArF- and 157 Nm F2-Lasers are based on polymers having anthracene (derivative), hydroxyalkyl, oxiranylalkyl, and, optionally, Me side chains and optionally contain suitable anthracene (derivative) chromophores. A typical polymer was manufactured by radical polymerization of 9-anthrylmethyl acrylate 0.5, 2-hydroxyethyl acrylate 0.3, and glycidyl methacrylate 0.2 mol.

IT 294673-25-9P 294673-27-1P 294673-28-2P
294673-29-3P 294673-30-6P 294673-31-7P
294673-32-8P 294673-33-9P 294673-34-0P
294673-35-1P 294673-36-2P 294673-37-3P
294673-38-4P 294673-39-5P 294673-41-9P
294673-42-0P 294673-43-1P 294673-44-2P
294673-45-3P 294673-46-4P

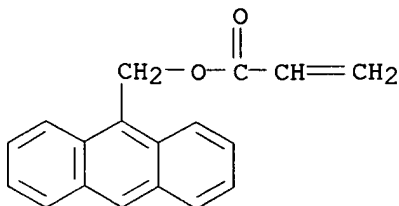
RL: IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (acrylic antireflective coatings for use in microlithog. in fabrication of semiconductor devices)

RN 294673-25-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, oxiranylmethyl ester, polymer with 9-anthracenylmethyl 2-propenoate and 2-hydroxyethyl 2-propenoate (9CI) (CA INDEX NAME)

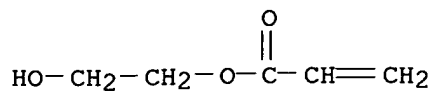
CM 1

CRN 31645-34-8
CMF C18 H14 O2



CM 2

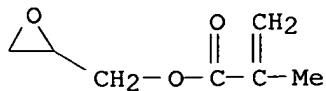
CRN 818-61-1
CMF C5 H8 O3



CM 3

CRN 106-91-2

CMF C7 H10 O3



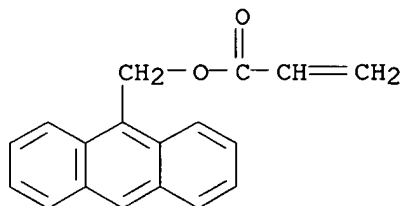
RN 294673-27-1 CAPLUS

CN 2-Propenoic acid, 2-methyl-, oxiranylmethyl ester, polymer with
9-anthracenylmethyl 2-propenoate and 3-hydroxypropyl 2-propenoate (9CI)
(CA INDEX NAME)

CM 1

CRN 31645-34-8

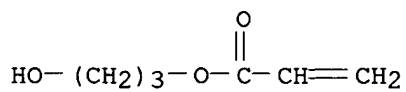
CMF C18 H14 O2



CM 2

CRN 2761-08-2

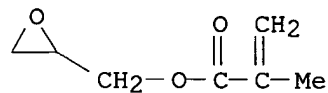
CMF C6 H10 O3



CM 3

CRN 106-91-2

CMF C7 H10 O3



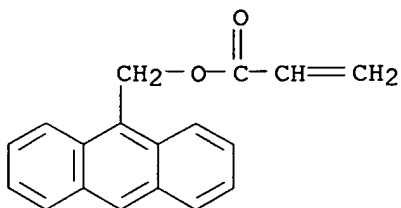
RN 294673-28-2 CAPLUS

CN 2-Propenoic acid, 9-anthracenylmethyl ester, polymer with 2-hydroxyethyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-34-8

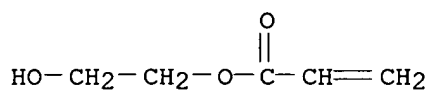
CMF C18 H14 O2



CM 2

CRN 818-61-1

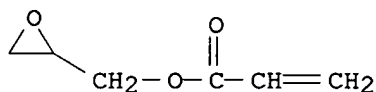
CMF C5 H8 O3



CM 3

CRN 106-90-1

CMF C6 H8 O3



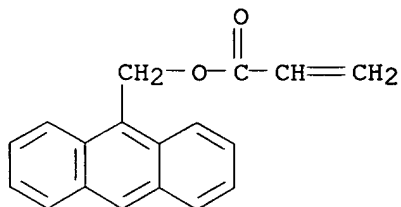
RN 294673-29-3 CAPLUS

CN 2-Propenoic acid, 9-anthracenylmethyl ester, polymer with 3-hydroxypropyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-34-8

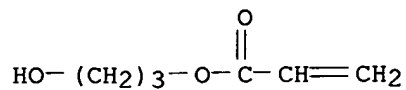
CMF C18 H14 O2



CM 2

CRN 2761-08-2

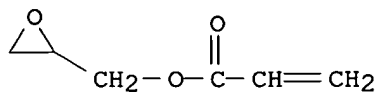
CMF C6 H10 O3



CM 3

CRN 106-90-1

CMF C6 H8 O3



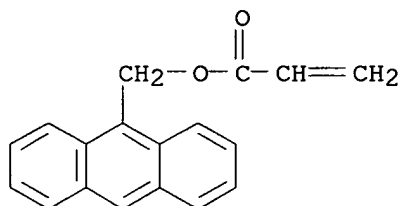
RN 294673-30-6 CAPLUS

CN 2-Propenoic acid, 9-anthracenylmethyl ester, polymer with 4-hydroxybutyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-34-8

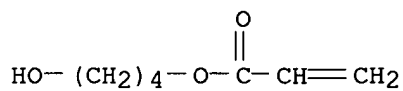
CMF C18 H14 O2



CM 2

CRN 2478-10-6

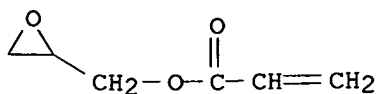
CMF C7 H12 O3



CM 3

CRN 106-90-1

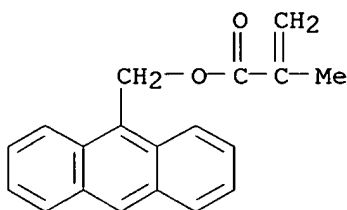
CMF C6 H8 O3



RN 294673-31-7 CAPLUS
 CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
 2-hydroxyethyl 2-propenoate and oxiranylmethyl 2-methyl-2-propenoate (9CI)
 (CA INDEX NAME)

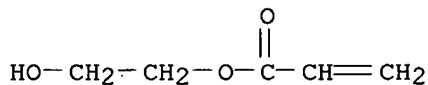
CM 1

CRN 31645-35-9
 CMF C19 H16 O2



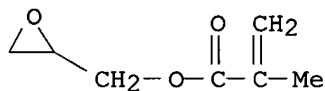
CM 2

CRN 818-61-1
 CMF C5 H8 O3



CM 3

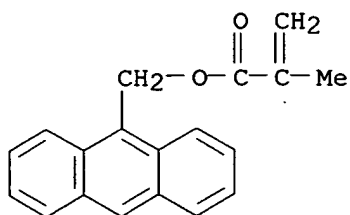
CRN 106-91-2
 CMF C7 H10 O3



RN 294673-32-8 CAPLUS
 CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
 3-hydroxypropyl 2-propenoate and oxiranylmethyl 2-methyl-2-propenoate
 (9CI) (CA INDEX NAME)

CM 1

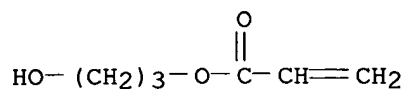
CRN 31645-35-9
 CMF C19 H16 O2



CM 2

CRN 2761-08-2

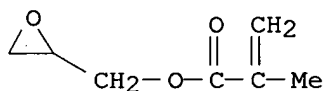
CMF C6 H10 O3



CM 3

CRN 106-91-2

CMF C7 H10 O3



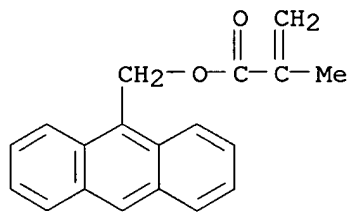
RN 294673-33-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
4-hydroxybutyl 2-propenoate and oxiranylmethyl 2-methyl-2-propenoate (9CI)
(CA INDEX NAME)

CM 1

CRN 31645-35-9

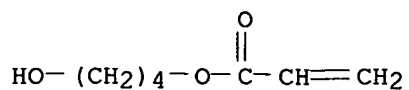
CMF C19 H16 O2



CM 2

CRN 2478-10-6

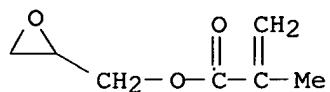
CMF C7 H12 O3



CM 3

CRN 106-91-2

CMF C7 H10 O3



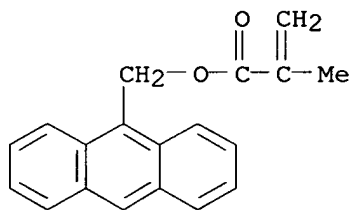
RN 294673-34-0 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with 2-hydroxyethyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

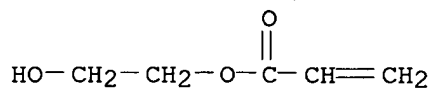
CMF C19 H16 O2



CM 2

CRN 818-61-1

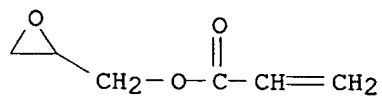
CMF C5 H8 O3



CM 3

CRN 106-90-1

CMF C6 H8 O3



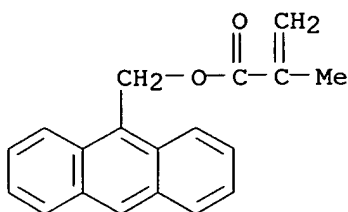
RN 294673-35-1 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
3-hydroxypropyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA
INDEX NAME)

CM 1

CRN 31645-35-9

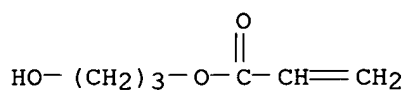
CMF C19 H16 O2



CM 2

CRN 2761-08-2

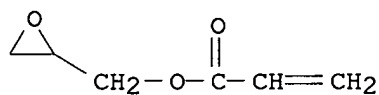
CMF C6 H10 O3



CM 3

CRN 106-90-1

CMF C6 H8 O3



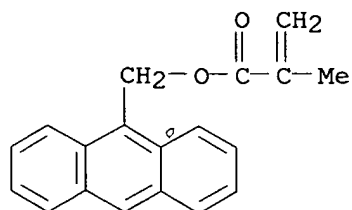
RN 294673-36-2 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
4-hydroxybutyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA
INDEX NAME)

CM 1

CRN 31645-35-9

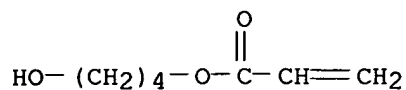
CMF C19 H16 O2



CM 2

CRN 2478-10-6

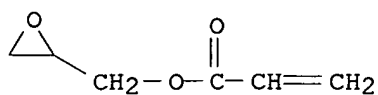
CMF C7 H12 O3



CM 3

CRN 106-90-1

CMF C6 H8 O3



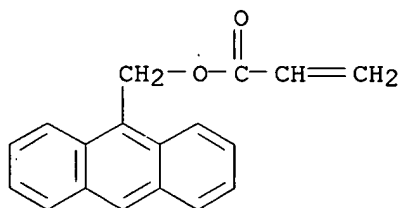
RN 294673-37-3 CAPLUS

CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with
9-anthracenylmethyl 2-propenoate, 2-hydroxyethyl 2-propenoate and
oxiranylmethyl 2-methyl-2-propenoate (9CI) . (CA INDEX NAME)

CM 1

CRN 31645-34-8

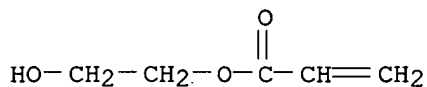
CMF C18 H14 O2



CM 2

CRN 818-61-1

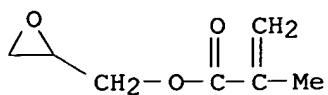
CMF C5 H8 O3



CM 3

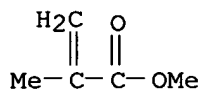
CRN 106-91-2

CMF C7 H10 O3



CM 4

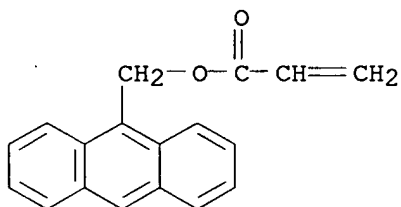
CRN 80-62-6
CMF C5 H8 O2



RN 294673-38-4 CAPLUS
CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with
9-anthracenylmethyl 2-propenoate, 3-hydroxypropyl 2-propenoate and
oxiranylmethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

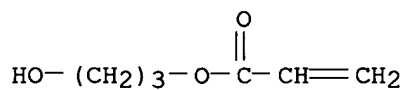
CM 1

CRN 31645-34-8
CMF C18 H14 O2



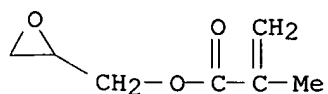
CM 2

CRN 2761-08-2
CMF C6 H10 O3



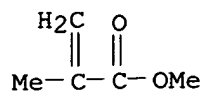
CM 3

CRN 106-91-2
CMF C7 H10 O3



CM 4

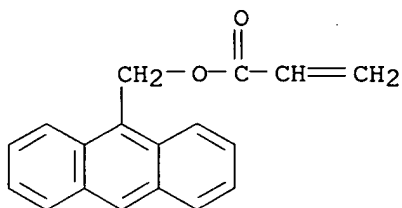
CRN 80-62-6
CMF C5 H8 O2



RN 294673-39-5 CAPLUS
CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with
9-anthracenylmethyl 2-propenoate, 2-hydroxyethyl 2-propenoate and
oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

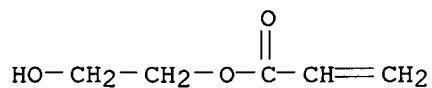
CM 1

CRN 31645-34-8
CMF C18 H14 O2



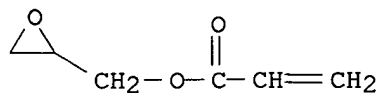
CM 2

CRN 818-61-1
CMF C5 H8 O3



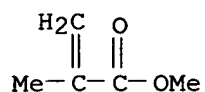
CM 3

CRN 106-90-1
CMF C6 H8 O3



CM 4

CRN 80-62-6
CMF C5 H8 O2



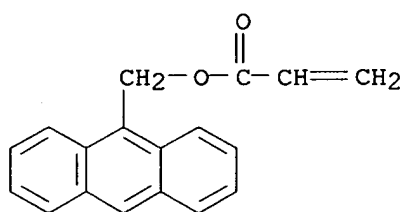
RN 294673-41-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with
9-anthracenylmethyl 2-propenoate, 4-hydroxybutyl 2-propenoate and
oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-34-8

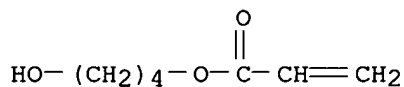
CMF C18 H14 O2



CM 2

CRN 2478-10-6

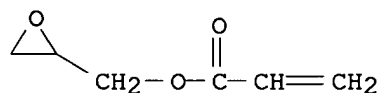
CMF C7 H12 O3



CM 3

CRN 106-90-1

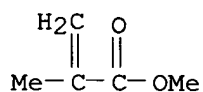
CMF C6 H8 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



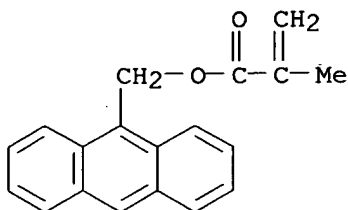
RN 294673-42-0 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
2-hydroxyethyl 2-propenoate, methyl 2-methyl-2-propenoate and
oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

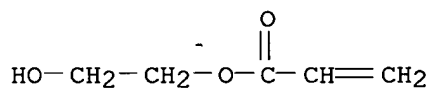
CMF C19 H16 O2



CM 2

CRN 818-61-1

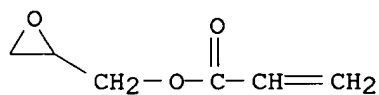
CMF C5 H8 O3



CM 3

CRN 106-90-1

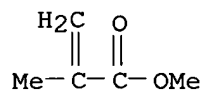
CMF C6 H8 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



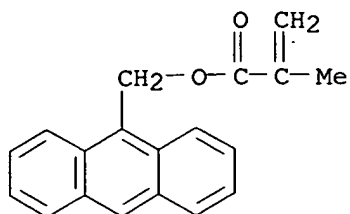
RN 294673-43-1 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with
3-hydroxypropyl 2-propenoate, methyl 2-methyl-2-propenoate and
oxiranylmethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

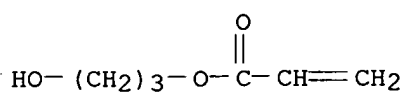
CMF C19 H16 O2



CM 2

CRN 2761-08-2

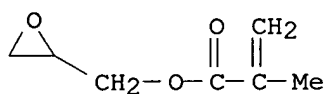
CMF C6 H10 O3



CM 3

CRN 106-91-2

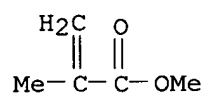
CMF C7 H10 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



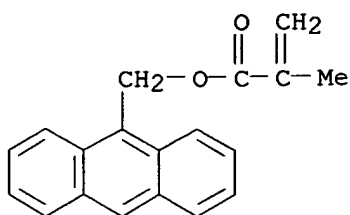
RN 294673-44-2 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with 4-hydroxybutyl 2-propenoate, methyl 2-methyl-2-propenoate and oxiranylmethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

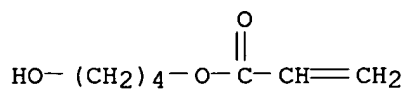
CMF C19 H16 O2



CM 2

CRN 2478-10-6

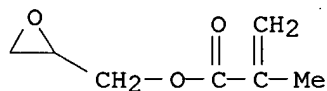
CMF C7 H12 O3



CM 3

CRN 106-91-2

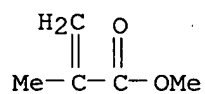
CMF C7 H10 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



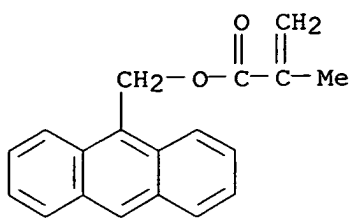
RN 294673-45-3 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with 3-hydroxypropyl 2-propenoate, methyl 2-methyl-2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

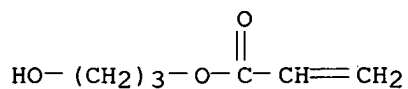
CMF C19 H16 O2



CM 2

CRN 2761-08-2

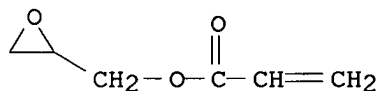
CMF C6 H10 O3



CM 3

CRN 106-90-1

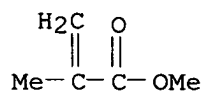
CMF C6 H8 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



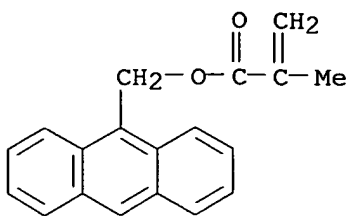
RN 294673-46-4 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with 4-hydroxybutyl 2-propenoate, methyl 2-methyl-2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-35-9

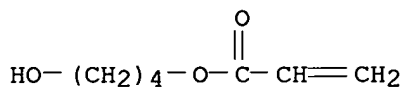
CMF C19 H16 O2



CM 2

CRN 2478-10-6

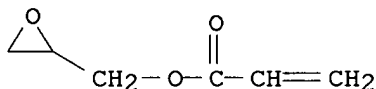
CMF C7 H12 O3



CM 3

CRN 106-90-1

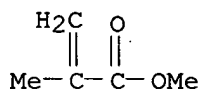
CMF C6 H8 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



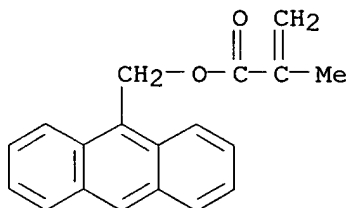
IT 31645-35-9P, 9-Anthrylmethyl methacrylate

RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(acrylic antireflective coatings for use in microlithog. in fabrication of semiconductor devices)

RN 31645-35-9 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester (CA INDEX NAME)



IT 294673-40-8P

RL: IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (binder; acrylic antireflective coatings for use in microlithog. in fabrication of semiconductor devices)

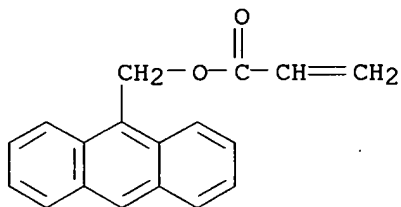
RN 294673-40-8 CAPLUS

CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with 9-anthracenylmethyl 2-propenoate, 3-hydroxypropyl 2-propenoate and oxiranylmethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 31645-34-8

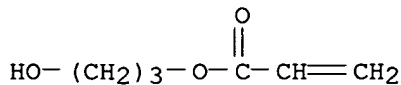
CMF C18 H14 O2



CM 2

CRN 2761-08-2

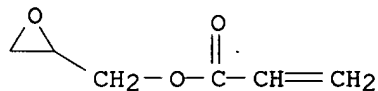
CMF C6 H10 O3



CM 3

CRN 106-90-1

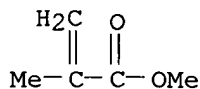
CMF C6 H8 O3



CM 4

CRN 80-62-6

CMF C5 H8 O2



IT 120-12-7, Anthracene, uses 577-33-3,

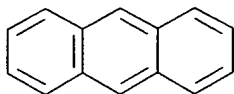
1,2,10-Anthracenetriol 642-31-9, 9-Anthraldehyde
723-62-6, 9-Anthracenecarboxylic acid 1143-38-0,
Dithranol 1210-12-4, 9-Anthracenecarbonitrile 18004-57-4
, 9-Anthraldehyde oxime 53531-31-0, 9-Anthryl trifluoromethyl
ketone

RL: MOA (Modifier or additive use); TEM (Technical or engineered material
use); USES (Uses)

(chromophore additive; acrylic antireflective coatings for use in
microlithog. in fabrication of semiconductor devices)

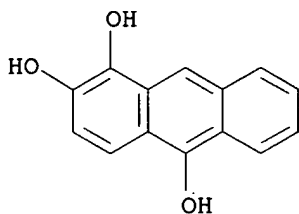
RN 120-12-7 CAPLUS

CN Anthracene (CA INDEX NAME)



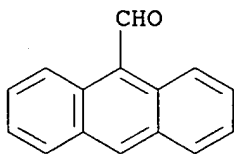
RN 577-33-3 CAPLUS

CN 1,2,10-Anthracenetriol (CA INDEX NAME)



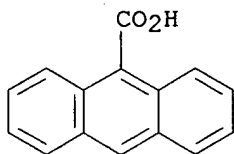
RN 642-31-9 CAPLUS

CN 9-Anthracenecarboxaldehyde (CA INDEX NAME)



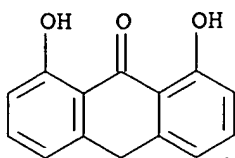
RN 723-62-6 CAPLUS

CN 9-Anthracenecarboxylic acid (CA INDEX NAME)

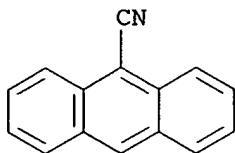


RN 1143-38-0 CAPLUS

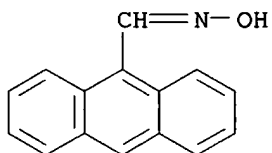
CN 9(10H)-Anthracenone, 1,8-dihydroxy- (CA INDEX NAME)



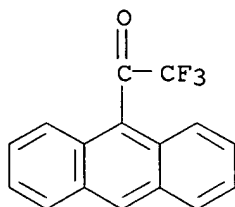
RN 1210-12-4 CAPLUS
CN 9-Anthracenecarbonitrile (CA INDEX NAME)



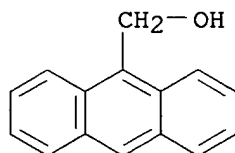
RN 18004-57-4 CAPLUS
CN 9-Anthracenecarboxaldehyde, oxime (CA INDEX NAME)



RN 53531-31-0 CAPLUS
CN Ethanone, 1-(9-anthracenyl)-2,2,2-trifluoro- (CA INDEX NAME)

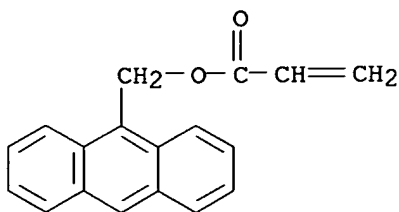


IT 1468-95-7, 9-Anthracenemethanol
RL: RCT (Reactant); RACT (Reactant or reagent)
(coating binder monomer precursor and chromophore additive;
acrylic antireflective coatings for use in microlithog. in fabrication
of semiconductor devices)
RN 1468-95-7 CAPLUS
CN 9-Anthracenemethanol (CA INDEX NAME)



IT 31645-34-8P, 9-Anthrylmethyl acrylate
RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
(Reactant or reagent)
(coating binder monomer; acrylic antireflective coatings for

use in microlithog. in fabrication of semiconductor devices)
RN 31645-34-8 CAPLUS
CN 2-Propenoic acid, 9-anthracenylmethyl ester (CA INDEX NAME)



L5 ANSWER 18 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
ACCESSION NUMBER: 1999:327012 CAPLUS
DOCUMENT NUMBER: 130:359300
TITLE: Antireflective coating composition containing photoacid generator, substrate having its coating layer, and manufacture of photoresist relief image using it
INVENTOR(S): Pavelchek, Edward K.; Docanto, Manuel
PATENT ASSIGNEE(S): Shipley Company L.L.C., USA
SOURCE: Jpn. Kokai Tokkyo Koho, 55 pp.
CODEN: JKXXAF
DOCUMENT TYPE: Patent
LANGUAGE: Japanese
FAMILY ACC. NUM. COUNT: 2
PATENT INFORMATION:

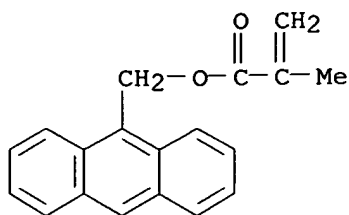
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 11133618	A	19990521	JP 1998-61845	19980206
JP 3408415	B2	20030519		
US 5939236	A	19990817	US 1997-797741	19970207
			US 1997-797741	A 19970207

PRIORITY APPLN. INFO.:
AB The composition for use with overcoated photoresists comprises (A) a resin binder, (B) an acid or thermal acid generator, and (C) a photoacid generator. The substrate is successively coated with the above composition layer and a photoresist layer. The photoresist relief image is manufactured by (1) successively applying the above composition and a photoresist composition on a substrate, (2) exposing the photoresist layer to activating radiation to generate acids from the photoacid generator, and (3) developing the exposed photoresist layer. The coating composition, particularly useful for deep UV applications in patterning semiconductor wafers, reduces undesired footing of overcoated resist relief images.

IT 161065-83-4P
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(antireflective coating composition containing photoacid generator used with overcoated photoresists for high-resolution resist reliefs without footing)
RN 161065-83-4 CAPLUS
CN 2-Propenoic acid, 2-methyl-, 9-anthracenylmethyl ester, polymer with 2-hydroxyethyl 2-methyl-2-propenoate (CA INDEX NAME)

CM 1

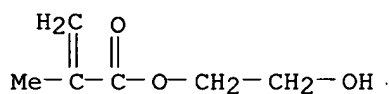
CRN 31645-35-9
CMF C19 H16 O2



CM 2

CRN 868-77-9

CMF C6 H10 O3



L5 ANSWER 19 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1989:644203 CAPLUS

DOCUMENT NUMBER: 111:244203

ORIGINAL REFERENCE NO.: 111:40347a,40350a

TITLE: Electrophotographic printing plate containing
naphthalocyanine or anthracyanine sensitizer

INVENTOR(S): Miyazaki, Shiyuji; Sakamoto, Mare; Suda, Yasumasa

PATENT ASSIGNEE(S): Toyo Ink Mfg. Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

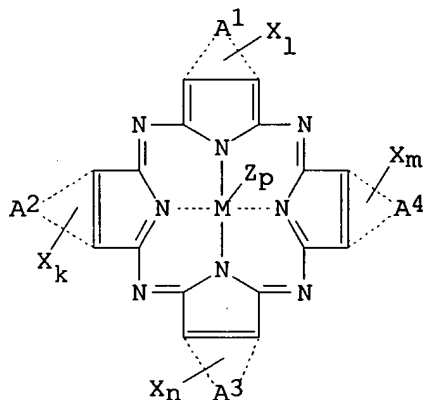
DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 01032270	A	19890202	JP 1987-188524	19870728
PRIORITY APPLN. INFO.: GI			JP 1987-188524	19870728



I

AB In the title printing plate, a photoconductive layer contains a

photoconductive Zn oxide, a binder resin, and ≥ 1 I [A1-A4
 = naphthalene ring, or anthracene ring; M = Group IA, IB, IIA, IIB, IIIA,
 IIIB, IVA, IVB, VB, VIB, VIIB, or VIII metal atom; Z = halo, O, OH, OR1,
 OSiR2R3R4; R1 = alkyl, aryl, acyl, cycloalkyl, polyether; R2, R3, R4 =
 alkyl, aryl, cycloalkyl, siloxyl, alkoxy; X = halo, OH, alkyl, aryl,
 heterocyclyl, OR5, SR5, NR6R7, SO2NR8R9, CH2NHCOCH2NR8R9, COOR9, NO2,
 SO3H, CN; R5 = R1; R6, R7 = H, alkyl, cycloalkyl, aryl; R6 and R7 may form
 a N-containing 4-7-membered heterocyclic ring; R8 = H, alkyl; R9 = H, alkyl,
 aryl, heterocyclyl, R10NR11R12; R10-R12 = alkyl; R11 and R12 may form a N,
 O, or S-containing heterocyclic ring; p = 0-2; k, l, m, n = 0-8]. The
 printing plate is sensitive to a semiconductor laser.

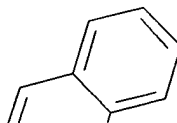
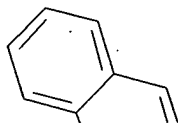
IT 40925-31-3

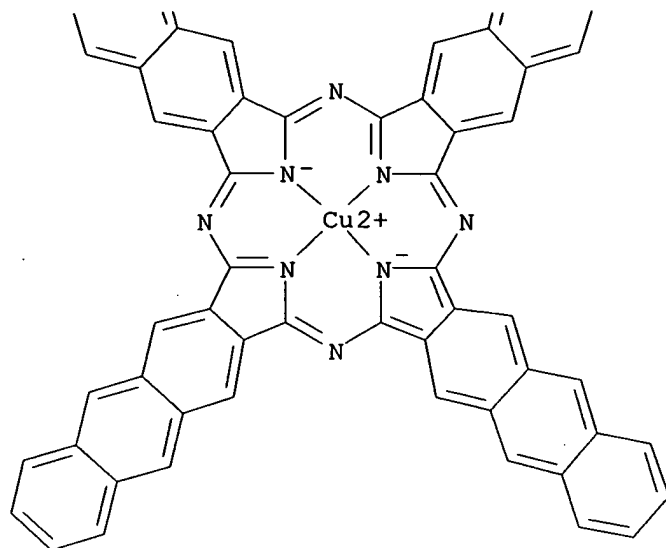
RL: DEV (Device component use); USES (Uses)
 (electrophotog. printing plate containing, as sensitizer)

RN 40925-31-3 CAPLUS

CN Copper, [37H,39H-tetranaphtho[2,3-b:2',3'-g:2'',3''-l:2''',3'''-
 q]porphyrazinato(2-)-N37,N38,N39,N40]-, (SP-4-1)- (9CI) (CA INDEX NAME)

PAGE 1-A





L5 ANSWER 20 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1989:85352 CAPLUS

DOCUMENT NUMBER: 110:85352

ORIGINAL REFERENCE NO.: 110:13951a,13954a

TITLE: Laminated electrophotographic photoreceptor with charge transporting layer containing tetramethylbenzene

INVENTOR(S): Yasumori, Akiyoshi; Enomoto, Takamichi; Kato, Tatsuya

PATENT ASSIGNEE(S): Ricoh Co., Ltd., Japan

SOURCE: Jpn. Tokkyo Koho, 4 pp.

CODEN: JAXXAD

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 63026379	B	19880530	JP 1978-68096	19780606
JP 54158928	A	19791215		

PRIORITY APPLN. INFO.: JP 1978-68096 A 19780606

AB In a composite-type electrophotog. photoreceptor in which a charge-generating layer comprising a p-type semiconductor and a resin binder and a charge-transporting layer comprising an electron donor and a resin binder are successively deposited on a conductive support, tetramethylbenzene is incorporated in the charge transporting layer. The photoreceptor shows good initial electrostatic characteristic and good durability.

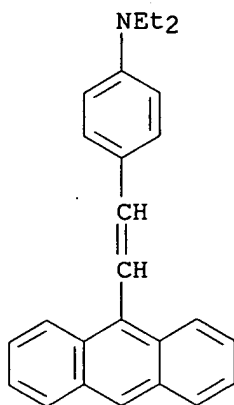
IT 71530-63-7

RL: USES (Uses)

(electrophotog. photoreceptor charge-transporting layer containing)

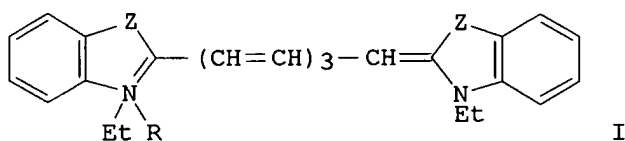
RN 71530-63-7 CAPLUS

CN Benzenamine, 4-[2-(9-anthracenyl)ethenyl]-N,N-diethyl- (CA INDEX NAME)



L5 ANSWER 21 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN
 ACCESSION NUMBER: 1984:129860 CAPLUS
 DOCUMENT NUMBER: 100:129860
 ORIGINAL REFERENCE NO.: 100:19660h,19661a
 TITLE: Electrophotographic photosensitive material
 PATENT ASSIGNEE(S): Fujitsu Ltd., Japan
 SOURCE: Jpn. Kokai Tokkyo Koho, 5 pp.
 CODEN: JKXXAF
 DOCUMENT TYPE: Patent
 LANGUAGE: Japanese
 FAMILY ACC. NUM. COUNT: 1
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 58181053	A	19831022	JP 1982-63379	19820416
PRIORITY APPLN. INFO.: GI			JP 1982-63379	19820416



AB The electrophotog. material has a supported layer containing (1) a photoconductive composition prepared by treating a photoconductive material with a sensitizing dye and a 1st charge-transfer compound in that order, (2) a 2nd charge-transfer compound, and (3) a resin. Compound I (Z = S, C, R = I, Br) is an example of a preferable sensitizing dye, and phthalocyanine is an example of the photoconductive material. This composition provides high sensitivity and high charge voltage in spite of using the relatively insensitive Cu phthalocyanine-binder system. Thus, Cu phthalocyanine (Lionol Blue SM, Dainippon Ink & Chemical) was treated with 1,1'-diethyl-11-bromo-4,4'-quinodimethane bromide (NK-1950, Japanese Inst. for Photosensitizing Dyes, Co.) in a dispersion in MeOH, separated and again similarly treated in benzene/iso-PrOH solvent with 2,5-bis(4'-diethylaminophenyl)-1,3,4-oxadiazole. The treated Cu phthalocyanine 10 was mixed with poly(N-vinylcarbazole) 2 and polyester resin (Polyester Adhesive 49,000, Du Pont) 16 in THF to obtain a coating solution. Photosensitive material using this composition was chargeable to 1.5

times higher voltage compared to a material using untreated Cu phthalocyanine and was sensitive to ≥ 900 nm light including semiconductor laser light.

IT 29659-51-6

RL: USES (Uses)

(electrophotog. photoconductive composition containing cyanine dye- and charge

transfer compound-treated copper phthalocyanine and)

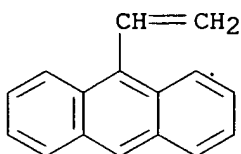
RN 29659-51-6 CAPLUS

CN Anthracene, 9-ethenyl-, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 2444-68-0

CMF C16 H12



L5 ANSWER 22 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1983:566984 CAPLUS

DOCUMENT NUMBER: 99:166984

ORIGINAL REFERENCE NO.: 99:25477a,25480a

TITLE: Electrophotographic photosensitive materials

PATENT ASSIGNEE(S): Canon K. K., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 3 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 57136655	A	19820823	JP 1981-23342	19810219
PRIORITY APPLN. INFO.:			JP 1981-23342	19810219

AB Electrophotog. plates are described which have a photoconductor layer composed of amorphous Si, a chalcogen type inorg. photoconductor, and a thermoplastic acrylic resin binder, and a 2nd photoconductor layer from an organic semiconductor. The electrophotog. plates exhibit good spectral sensitivity and good heat resistance. Thus, an Al cylinder was coated with a composition composed of amorphous Si 50, As₂Se₃ 40, and an acrylic resin (CMZ-20 from Fujikura Kasei K. K.) 20 parts, then coated with a poly(vinylcarbazole) solution, and fitted with a thermally shrinkable polyester tube to give an electrophotog. drum having excellent spectral sensitivity, and good moisture and heat resistances.

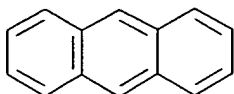
IT 120-12-7, uses and miscellaneous

RL: USES (Uses)

(electrophotog. plate with photoconductor layer containing amorphous silicon, chalcogen and)

RN 120-12-7 CAPLUS

CN Anthracene (CA INDEX NAME)



L5 ANSWER 23 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1980:613348 CAPLUS
 DOCUMENT NUMBER: 93:213348
 ORIGINAL REFERENCE NO.: 93:33919a, 33922a
 TITLE: Multilayer electrophotographic plates
 PATENT ASSIGNEE(S): Ricoh Co., Ltd., Japan
 SOURCE: Jpn. Kokai Tokkyo Koho, 4 pp.
 CODEN: JKXXAF
 DOCUMENT TYPE: Patent
 LANGUAGE: Japanese
 FAMILY ACC. NUM. COUNT: 1
 PATENT INFORMATION:

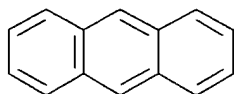
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 55060955	A	19800508	JP 1978-134117	19781031
PRIORITY APPLN. INFO.:			JP 1978-134117	A 19781031

AB A multilayer electrophotog. plate is composed of (1) a conductor support; (2) an N-type charge transfer layer whose main constituent is an electron acceptor; (3) a N-type charge generating layer made of ZnO, binder, and a sensitizer; (4) a P-type charge generating layer made of a P-type semiconductor, and (5) a P-type charge-transfer layer whose main constituent is an electron donor. The order of the above layer may be reversed. Thus, an Al laminated polyester film support was coated with (1) a tetranitrofluoroenone-polystyrene layer, (2) a ZnO-based composition layer containing acrylic resin, Rose Bengal, and Tetrabromophenol Blue, (3) an amorphous Se layer, and (4) a poly(vinylcarboazole) layer to give an electrophotog. plate with excellent panchromatic sensitivity.

IT 75429-11-7
 RL: DEV (Device component use); USES (Uses)
 (multilayer electrophotog. plate containing)

RN 75429-11-7 CAPLUS

CN Anthracene, (2-phenylethenyl)- (9CI) (CA INDEX NAME)



D1- CH=CH- Ph

L5 ANSWER 24 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1979:620313 CAPLUS
 DOCUMENT NUMBER: 91:220313
 ORIGINAL REFERENCE NO.: 91:35359a, 35362a
 TITLE: Development of charged images
 INVENTOR(S): Takasu, Yoshio; Hino, Takashi
 PATENT ASSIGNEE(S): Canon K. K., Japan
 SOURCE: Ger. Offen., 35 pp.
 CODEN: GWXXBX
 DOCUMENT TYPE: Patent
 LANGUAGE: German

FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 2854825	A1	19790628	DE 1978-2854825	19781219
DE 2854825	C2	19881117		
JP 54086335	A	19790709	JP 1977-154630	19771222
JP 63025337	B	19880525		
US 4258116	A	19810324	US 1978-968205	19781211

PRIORITY APPLN. INFO.:
JP 1977-154630 A 19771222
JP 1977-154631 A 19771222

AB Developer compns. for use in electrog. or electrophotog. consist of fine toner particles containing an organic semiconductor (≥ 0.1 weight parts/100 weight parts binder resin) which are supported on a dispenser surface of a metal or inorg. semiconductor and which in an elec. field take on a carrier-injection-induced charge of opposite polarity to that of the charge images 5μ to 5 mm away from the dispenser surface. Thus, a toner of $11.5\text{-}\mu$ particles of poly(9-vinylcarbazole) 10, polystyrene 40, magnetite 20, and carbon black 1 weight part dispensed from a rotating magnetized drum coated with Cu_2O on Al and set at $120\text{-}\mu$ from the charge-image drum with ZnO paper gave on application of an elec. field images with D_{max} 1.20 and fog d. 0.05 after 1 copy and 1.19 and 0.05 after 100 copies as compared to 0.20 and 0.08 for 1 copy and 0.22 and 0.09 for 100 copies, resp., for a toner of $20\text{-}\mu$ particles of polystyrene 100 and magnetite 40 weight parts.

IT 37372-26-2

RL: USES (Uses)

(toners containing, for electrostatog. developers)

RN 37372-26-2 CAPLUS

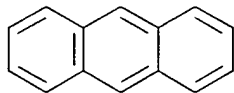
CN Anthracene, ethenyl-, homopolymer (CA INDEX NAME)

CM 1

CRN 30521-30-3

CMF C16 H12

CCI IDS



D1- $\text{CH}=\text{CH}_2$

L5 ANSWER 25 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1972:128986 CAPLUS

DOCUMENT NUMBER: 76:128986

ORIGINAL REFERENCE NO.: 76:20879a,20882a

TITLE: Semiconductor compounds for coating substrates

INVENTOR(S): Perez-Albuerne, Evelio A.

PATENT ASSIGNEE(S): Eastman Kodak Co.

SOURCE: Fr. Demande, 22 pp.

CODEN: FRXXBL

DOCUMENT TYPE: Patent

LANGUAGE: French

FAMILY ACC. NUM. COUNT: 5

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
FR 2058353	A5	19710528	FR 1970-30230	19700818
FR 2058353	B1	19760903		
US 3634336	A	19720111	US 1969-851088	19690818
PRIORITY APPLN. INFO.:			US 1969-851088	A 19690818

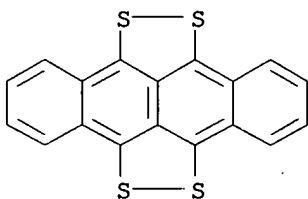
AB Polymeric substrates are coated with semiconductor compds. which are organic complexes comprising electron donors derived from polynuclear aromatic hydrocarbons having at least 2 atoms joined by a bridge containing 2-4 atoms of an element of Group VIb, such as S, Se, and Te, and electron acceptors which are either mineral or organic. Thus, a complex based on tetrathiotetracene (I) [193-44-2] was used. Aqueous I acetate containing about 10 mg/l. and 5 mg/l. gelatin were applied to a polyester surface. The film was then dried in a hot-air stream to give the semiconductor surface.

IT 193-44-2D, Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole, complexes with polystyrene sulfone 35201-34-4 36015-72-2 36452-11-6 36519-97-8 36529-19-8

RL: TEM (Technical or engineered material use); USES (Uses) (coatings, semiconducting)

RN 193-44-2 CAPLUS

CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (CA INDEX NAME)



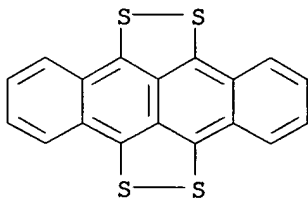
RN 35201-34-4 CAPLUS

CN 1,2-Benzenedicarboxylic acid, compd. with naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (9CI) (CA INDEX NAME)

CM 1

CRN 193-44-2

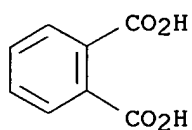
CMF C18 H8 S4



CM 2

CRN 88-99-3

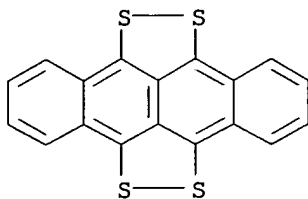
CMF C8 H6 O4



RN 36015-72-2 CAPLUS
 CN 2-Butenedioic acid (2Z)-, compd. with naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole (9CI) (CA INDEX NAME)

CM 1

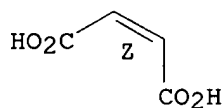
CRN 193-44-2
 CMF C18 H8 S4



CM 2

CRN 110-16-7
 CMF C4 H4 O4

Double bond geometry as shown.



RN 36452-11-6 CAPLUS
 CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiole, compd. with iodine (1:1) (9CI) (CA INDEX NAME)

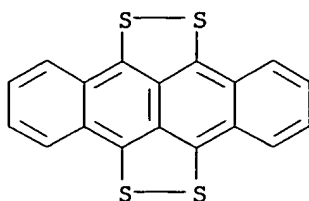
CM 1

CRN 7553-56-2
 CMF I2

I-I

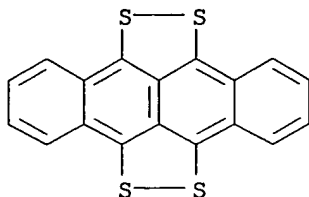
CM 2

CRN 193-44-2
 CMF C18 H8 S4



RN 36519-97-8 CAPLUS

CN Naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiolo, radical ion(1+), bromide
(9CI) (CA INDEX NAME)



● Br⁻

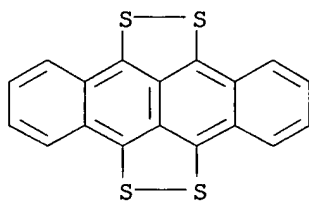
RN 36529-19-8 CAPLUS

CN Acetic acid, compd. with naphthaceno[5,6-cd:11,12-c'd']bis[1,2]dithiolo
(9CI) (CA INDEX NAME)

CM 1

CRN 193-44-2

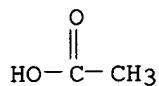
CMF C18 H8 S4



CM 2

CRN 64-19-7

CMF C2 H4 O2



L5 ANSWER 26 OF 26 CAPLUS COPYRIGHT 2008 ACS on STN

ACCESSION NUMBER: 1965:19667 CAPLUS

DOCUMENT NUMBER: 62:19667

ORIGINAL REFERENCE NO.: 62:3522e-f
 TITLE: Optically sensitized photoresistors
 INVENTOR(S): Weisbeck, Roland; Brockes, Andreas; Nassenstein, Heinrich
 PATENT ASSIGNEE(S): Farbenfabriken Bayer A.-G.
 SOURCE: 4 pp.
 DOCUMENT TYPE: Patent
 LANGUAGE: Unavailable
 FAMILY ACC. NUM. COUNT: 1
 PATENT INFORMATION:

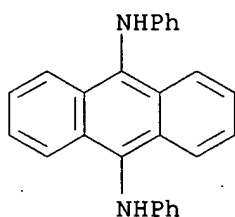
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 1180859		19641105	DE 1962-F38227	19621106
BE 638530			BE	
PRIORITY APPLN. INFO.:			DE	19621106

AB The spectral sensitivity of a photoresistor is extended toward shorter wavelengths by coating it with diisobutyl 3,9-perylenedicarboxylate (I) or 9,10-dianilinoanthracene (fluorescent compds. which emit radiation in the sensitivity range of the photoconductor) as a 0.1-1% dispersion in a transparent binder which as light conductor establishes the optical contact between the semiconductor and the fluorescent particles. In an example, the spectral sensitivity maximum of a CdS photoresistor is shifted from 605 to 590 mμ by a 40-mμ coating of a 0.2% dispersion of I in a colorless epoxy resin.

IT 2233-88-7, 9,10-Anthracenediamine, N,N'-diphenyl-
 (spectral sensitivity increase of CdS photo-resistors by)

RN 2233-88-7 CAPLUS

CN 9,10-Anthracenediamine, N9,N10-diphenyl- (CA INDEX NAME)



=>

---Logging off of STN---

=>

Executing the logoff script...

=> LOG Y

COST IN U.S. DOLLARS	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	147.86	327.10
DISCOUNT AMOUNTS (FOR QUALIFYING ACCOUNTS)	SINCE FILE ENTRY	TOTAL SESSION
CA SUBSCRIBER PRICE	-20.80	-20.80

STN INTERNATIONAL LOGOFF AT 17:28:40 ON 10 JUN 2008